

Some Interesting Self-assembled nano-structures of Pb/Si(111)

V. Yeh (葉旺奇)¹, M.K. Yakes^{2,3}, M. Hupalo², and M.C. Tringides²

1. Department of Physics, National Dong Hwa University, Hualien 97401, Taiwan.
2. Department of Physics, Iowa State University and Ames Laboratory--USDOE, Ames IA, 50011, USA.
3. Naval Research Lab, Washington D.C., USA



Outline

1. QSE driven growth mode
 - a. multi-layered islands
 - b. comparison between different interfaces
2. Stability of QSE driven islands
3. Applicability of nucleation theory
4. Low coverage structures

$\sqrt{3} \times \sqrt{3} - \beta$ $\sqrt{7} \times \sqrt{3}$ $\sqrt{43} \times \sqrt{3}$

$\sqrt{3} \times \sqrt{3} - \text{HIC}$ $\sqrt{3} \times \sqrt{3} - \text{SIC}$

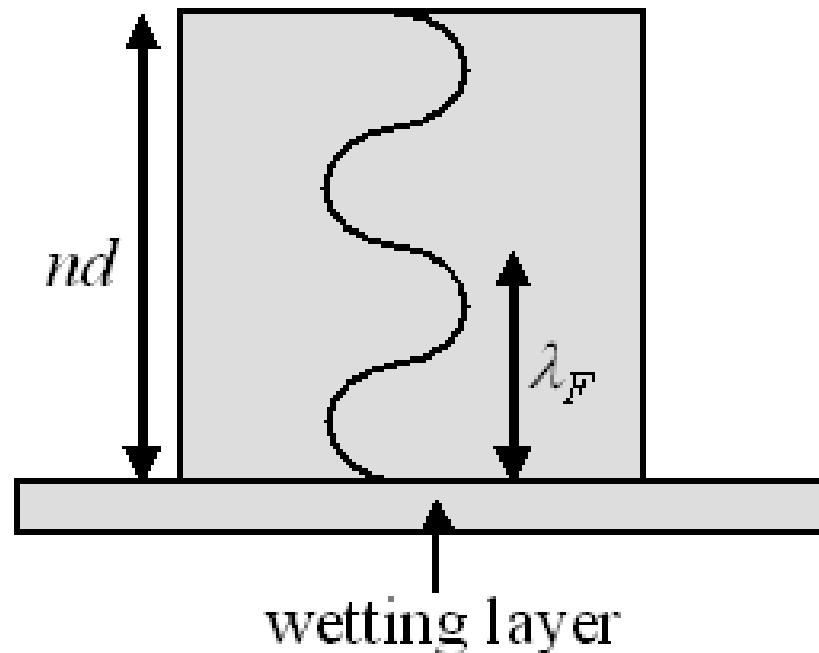
Anything else?

QSE
Driven
Growth Mode

Quantum size effects (QSE)

$$nd = s\lambda_F / 2 \quad (n, s \text{ integers})$$

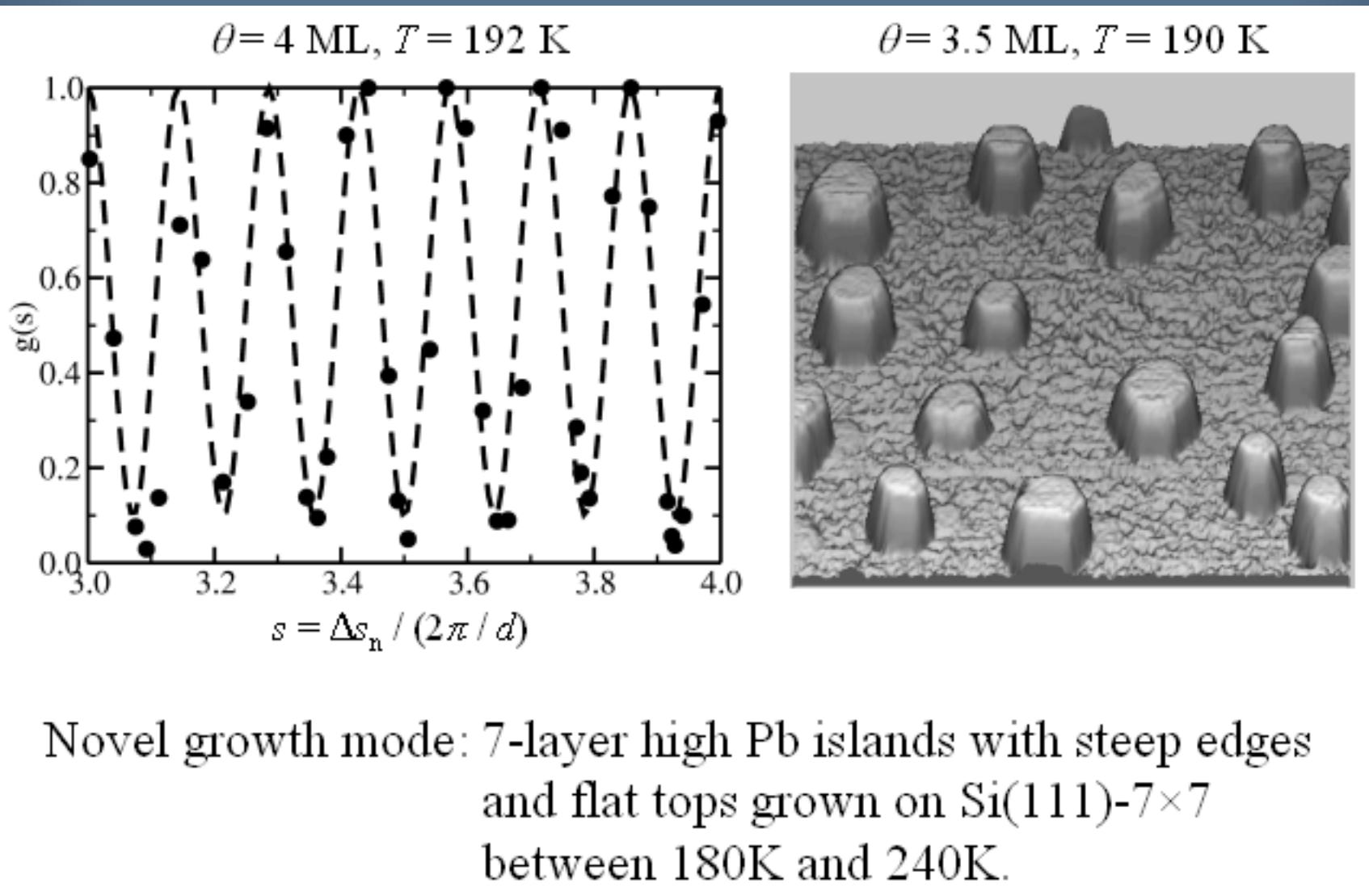
Vacuum



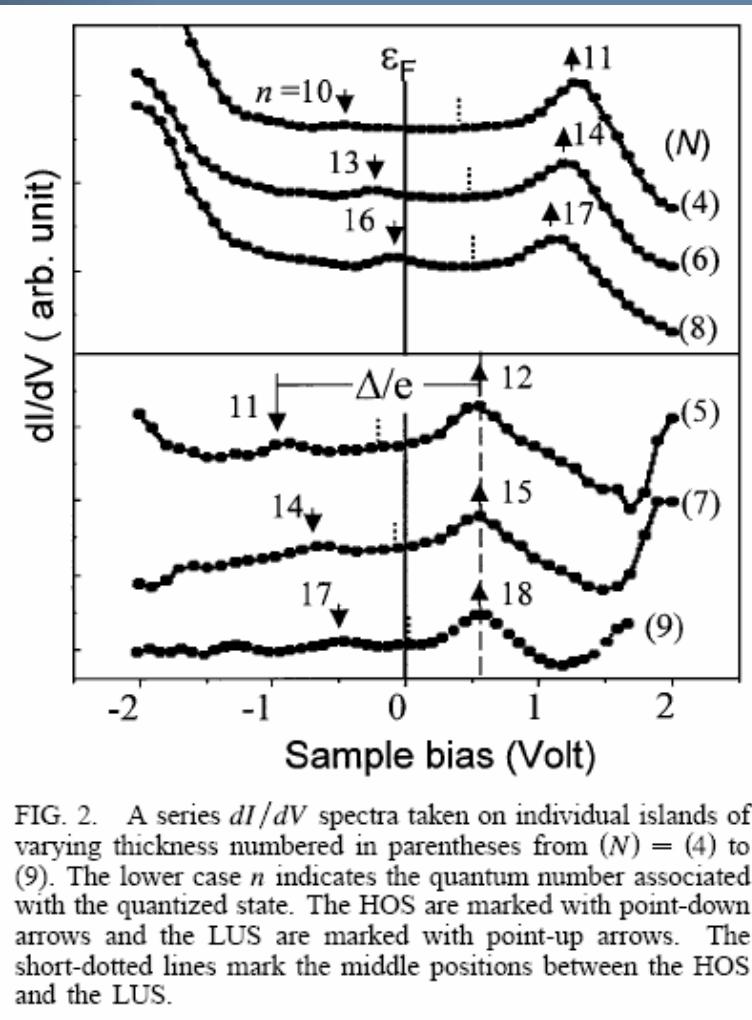
$$d = 0.286 \text{ nm}$$

$$\lambda_F = 0.395 \text{ nm}$$

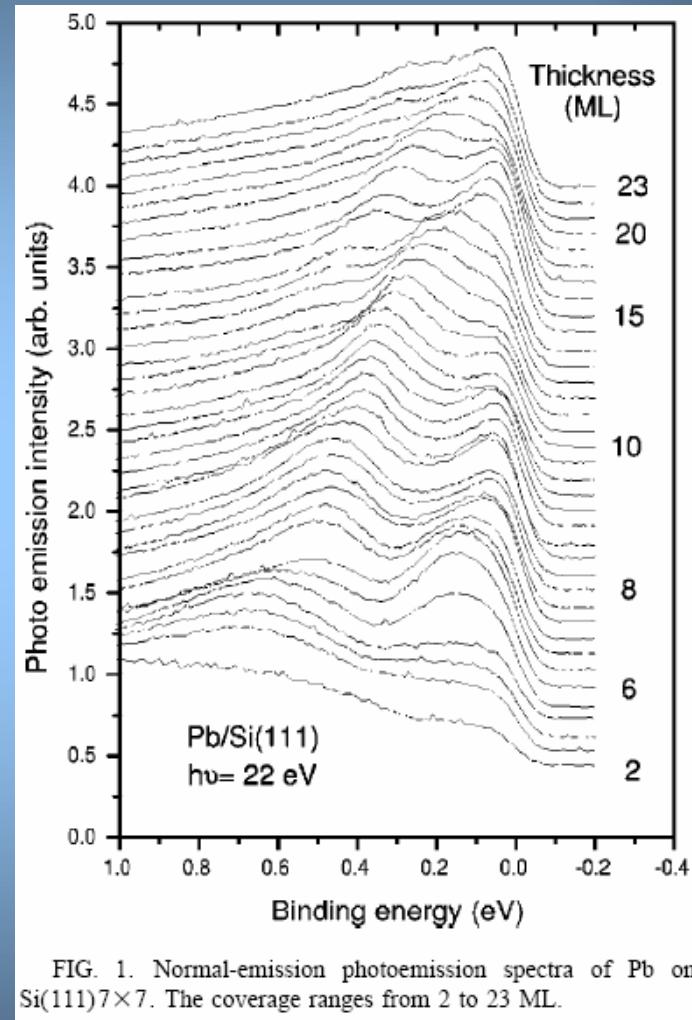
or
substrate



Quantum well states of Pb islands

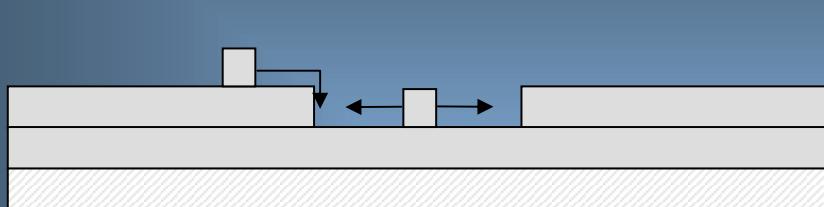


W.B. Su, S.H. Chang, W.B. Jian, C.S. Chang, L.J. Chen, and T.T. Tsong, PRL 86, 5116 (2001)



A. Mans*, J.H. Dil, and A. R. H. F. Ettema, H. H. Weitering, PRB 66, 194410 (2002)

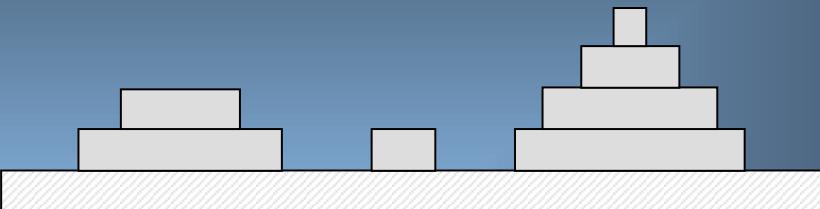
Different modes of thin film growth



Layer by layer

$$\Delta\gamma \leq 0$$

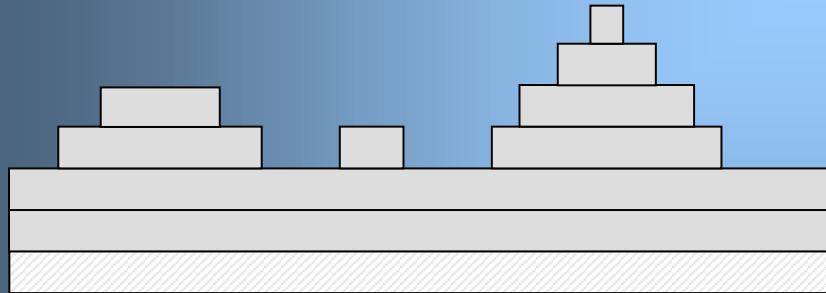
(Frank-van der Merwe)



Three dimensional

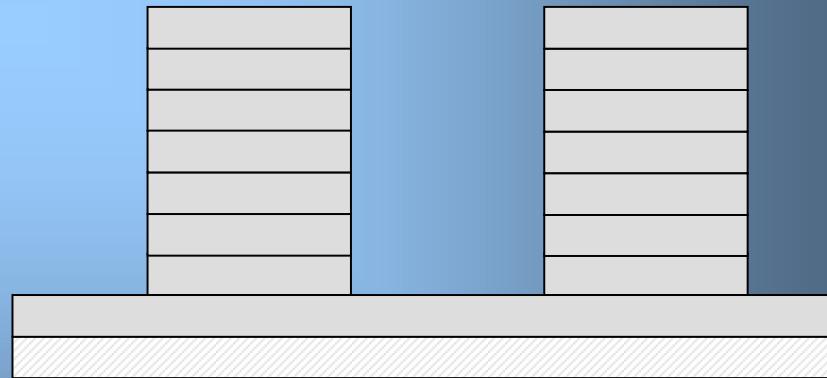
$$\Delta\gamma > 0$$

(Volmer-Weber)



Mixed

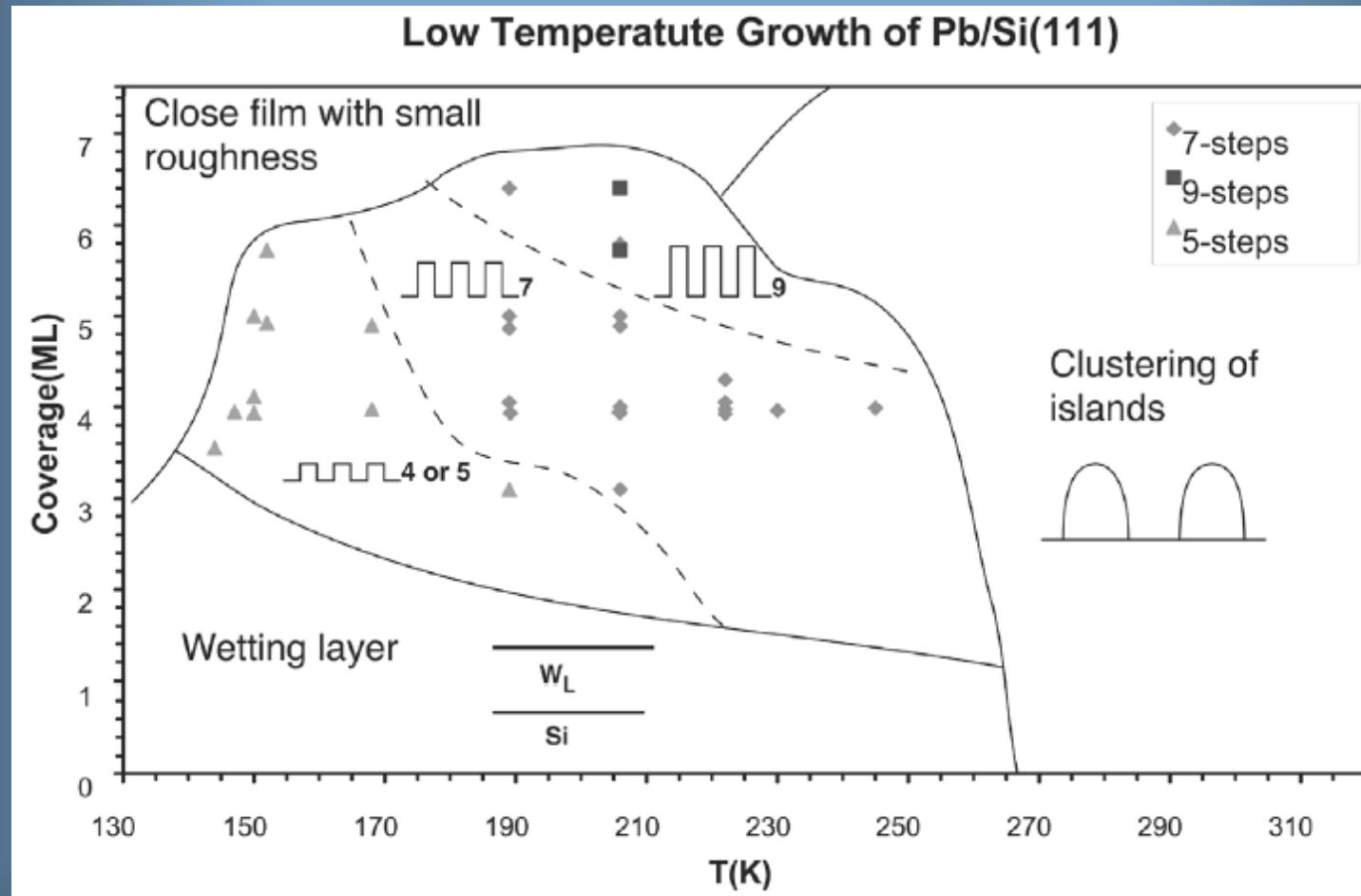
$\Delta\gamma < 0$, then change sign
(Stranski-Kratanov)



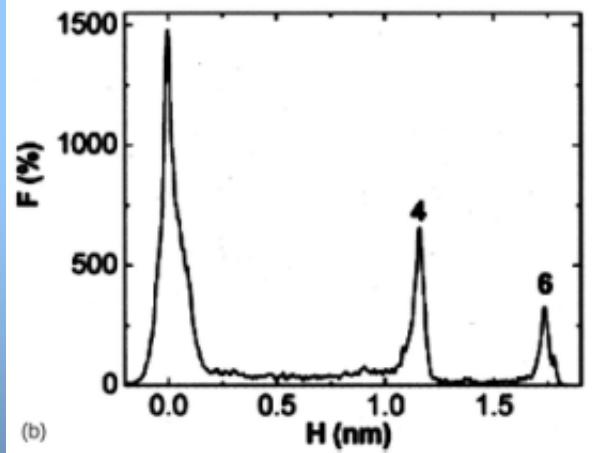
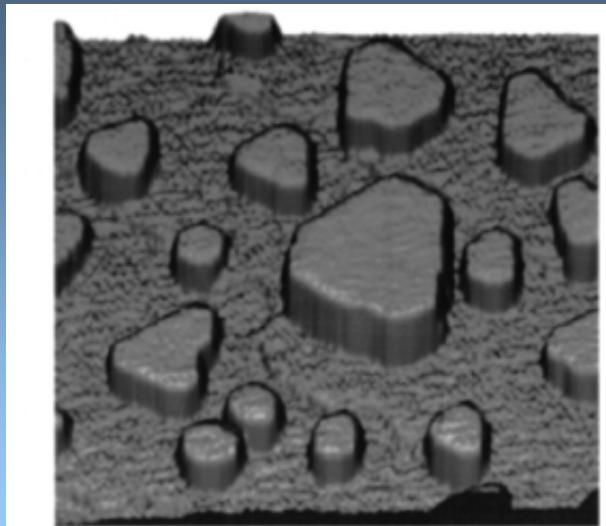
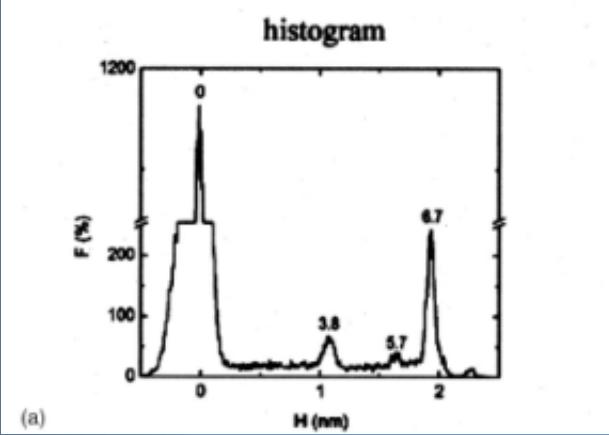
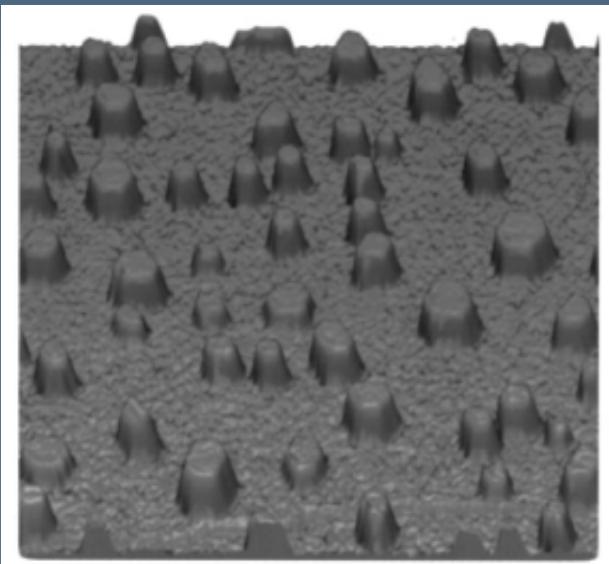
Newly discovered

7-layer high, flat top, steep edge
Quantum size effects (QSE)

Different stable heights with bi-layer difference under different conditions



Comparison
between
interfaces.



Si(111)-7 \times 7

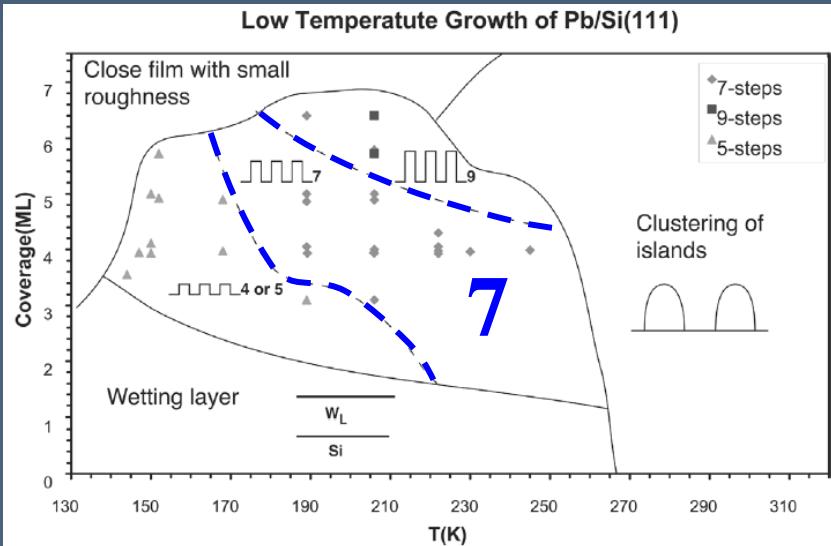
$\theta = 3.3$ ML

200 nm \times 200 nm

$T = 200$ K

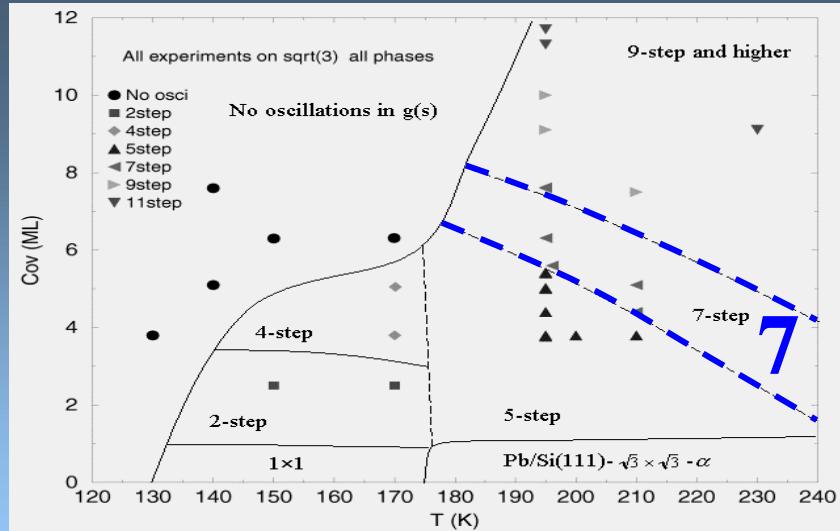
Pb/Si(111)- $\sqrt{3} \times \sqrt{3}$ - β

$\theta = 3$ ML



Si(111)-7x7

- Wetting layer: from 3 ML at 130K to 1 ML at RT
- 4- to 9-step islands observed
- For $\theta < 6$ ML and T between 190K and 200K, 7-step islands with mean size 90Å
- At T = 195K, islands tend to stay at 7-step and cover the whole surface at $\theta \sim 8$ ML, then new islands grow on top



Pb/Si(111)- $\sqrt{3} \times \sqrt{3}$

- First layer used to cover substrate to dense phase
- 2-step to 11-step islands observed
- For $\theta < 6$ ML and T between 190K and 200K, 5-step islands with mean size 180Å
- At T = 195K, islands tend to grow higher, in bi-layer increments, than grow larger for up to 20ML

$$E = E_0 - E_C$$

E_0 : the energy of the Pb film (after subtracting the bulk energy)

$E_C = C(\Delta E_f)^2$: energy gain due to the charge transfer

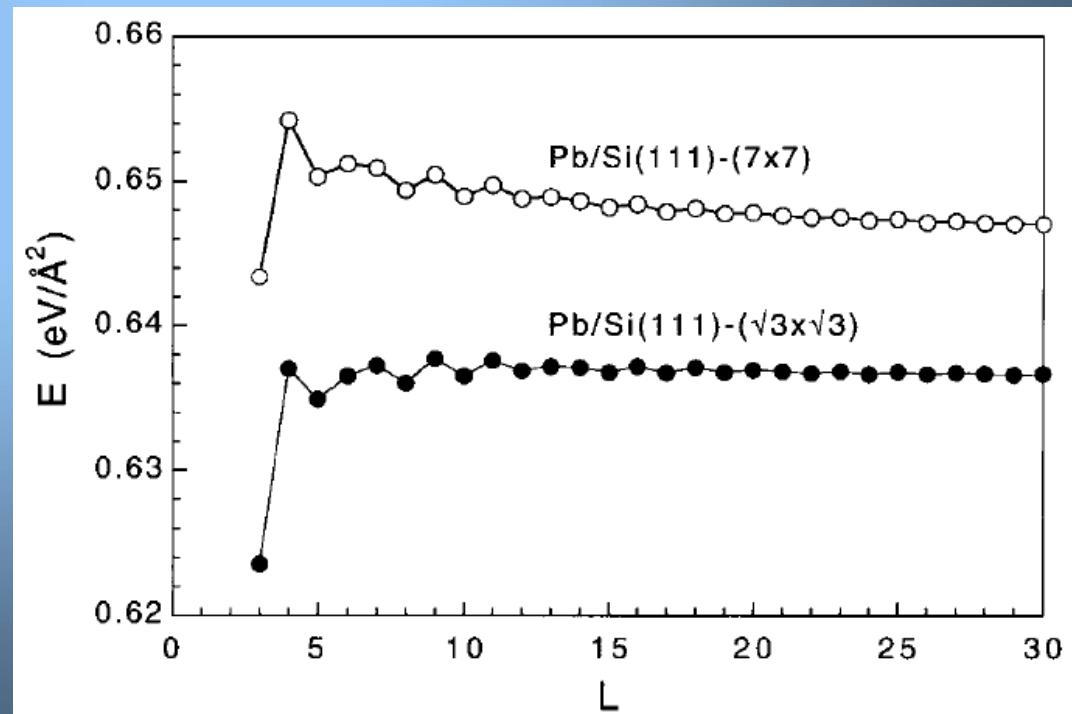
$\Delta E_f = 4.75 \text{ eV}$ for 7×7 and 4.98 eV for $\sqrt{3} \times \sqrt{3}$

$C = 0.033 \text{ eV}/\text{\AA}^2$

(see Zenyu Zhang, et al, PRL 80, 5381

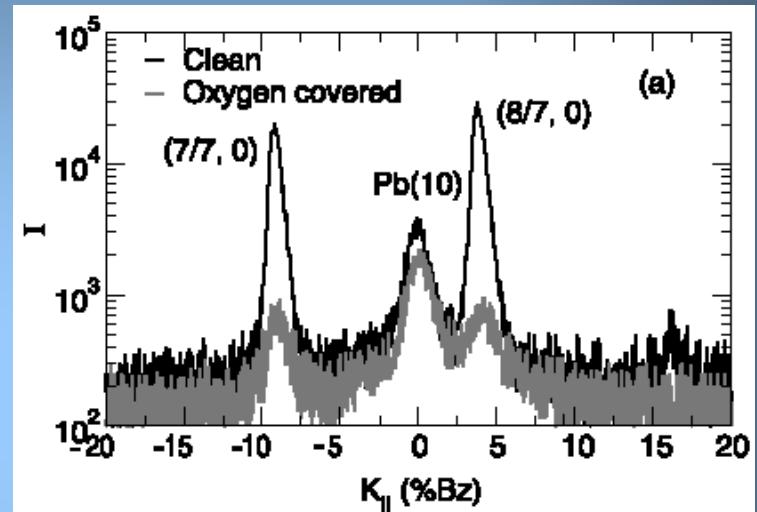
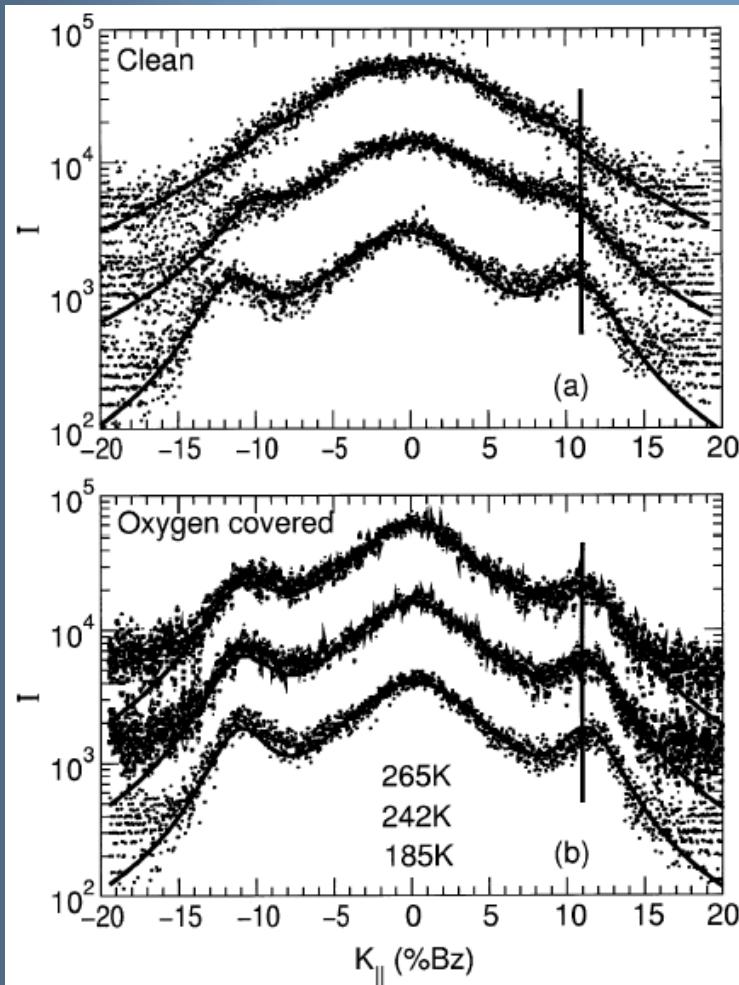
D.R. Heslina, et al, PRL 64, 1589 and H.H. Weitering, et al, PRB 45, 9126.)

Calculated film energy
vs film thickness L for
the two interfaces
showing the $\sqrt{3} \times \sqrt{3}$
phase has a lower curve
and different minima
due to larger charge
transfer term.



Stability
of
QSE driven islands.

Oxygen covered Pb islands retain their height to a higher temperature



Oxygen suppressed
atom diffusion to
the islands

Controlling the Thermal Stability of Thin Films by Interfacial Engineering

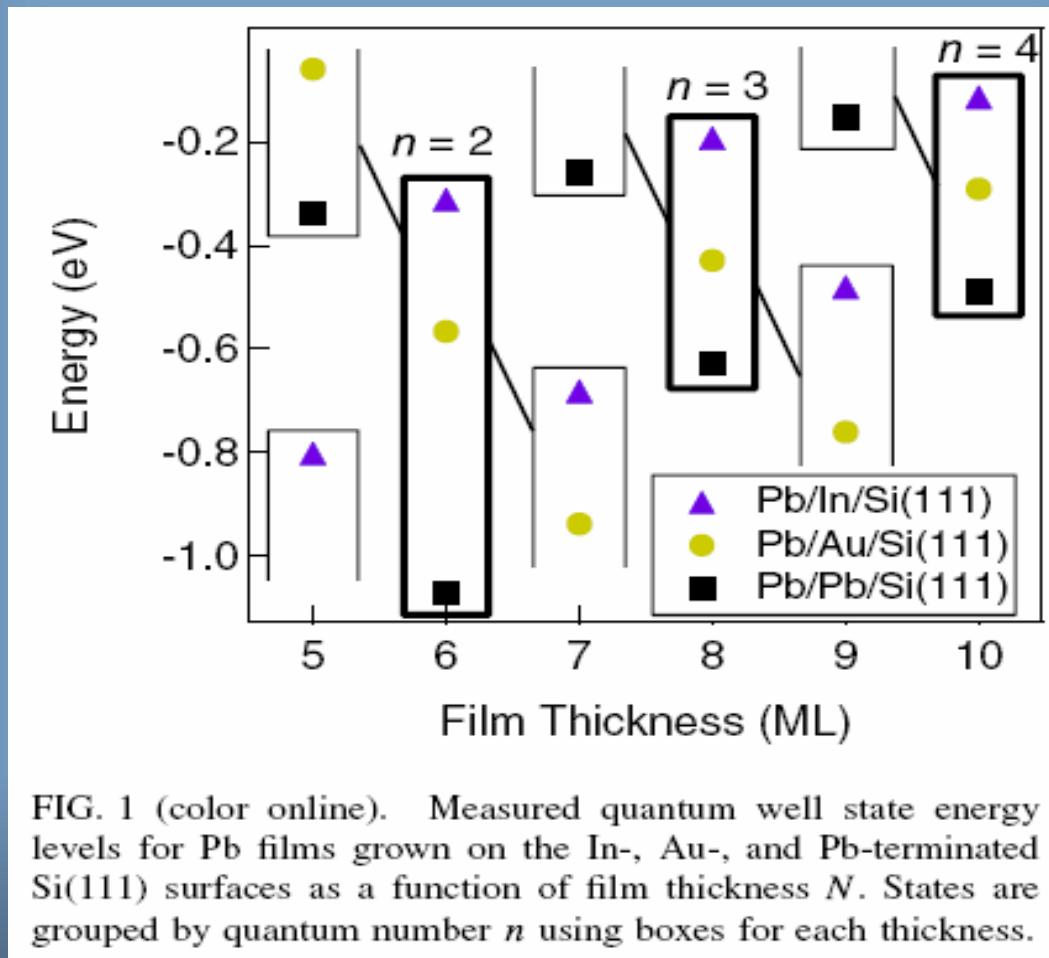


FIG. 1 (color online). Measured quantum well state energy levels for Pb films grown on the In-, Au-, and Pb-terminated Si(111) surfaces as a function of film thickness N . States are grouped by quantum number n using boxes for each thickness.

Applicability
of
nucleation theory.

For 2D islands and complete saturation

$$n_x = \eta(\theta, i) \left(\frac{D}{F} \right)^{-\chi} \exp \left(\frac{E_i}{(i+2)kT} \right) \quad \chi = \frac{i}{i+2}$$

$$\ln(n_x) = \ln \eta - \chi \ln \left(\frac{\nu_0}{4F} \right) + \frac{\chi}{kT} (E_m + \bar{E}_i)$$

$$\ln(n_x) = \chi \ln F + const 2$$

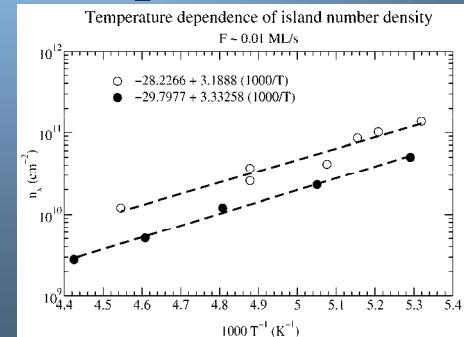
$$\ln(n_x) = \frac{\chi}{kT} (E_m + \bar{E}_i) + const.$$

$$s = \frac{\chi}{k} (E_m + \bar{E}_i)$$

$$\ln(n_x) \Big|_{1/T=0} = \ln \eta - \chi \ln \left(\frac{\nu_0}{4F} \right)$$

Rate dependence

Temperature
dependence



STM measurements

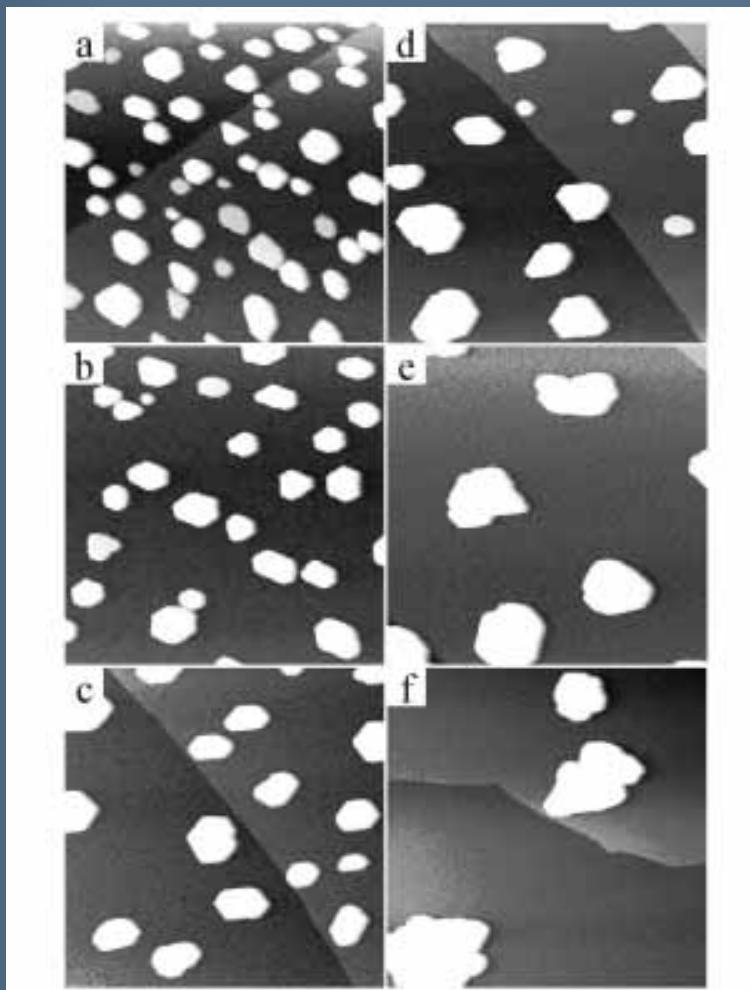


FIG. 5. The growth of Pb islands at (a) 189 K, (b) 198 K, (c) 208 K, (d) 217 K, (e) 226 K, and (f) 254 K at a coverage of 3.2 ML. The image size of (a)–(c) is $300 \times 300 \text{ nm}^2$, (d) and (e) is $500 \times 500 \text{ nm}^2$, (f) is $1000 \times 1000 \text{ nm}^2$.

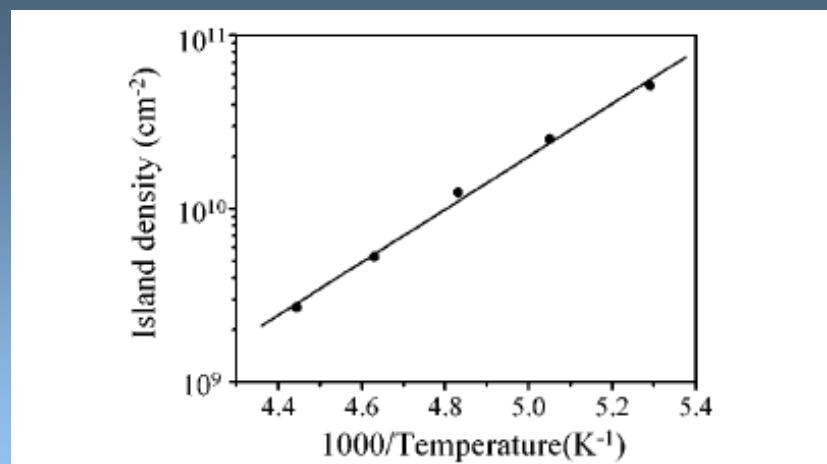


FIG. 6. The Arrhenius plot of the island density versus temperature, showing a linear relationship.

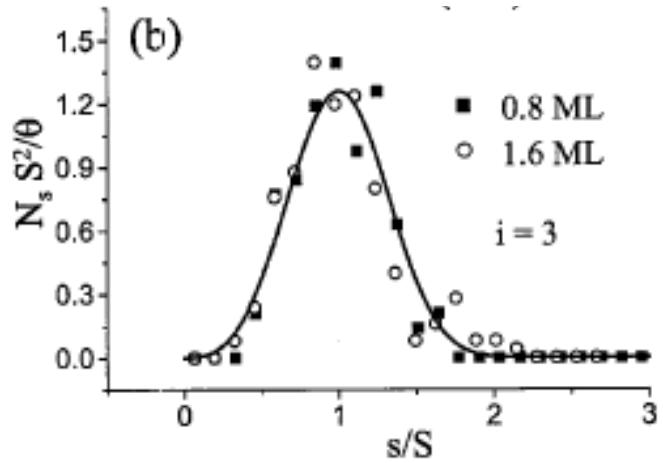


FIG. 4. (a) Pb island size distributions at the coverage of 0.8 and 1.6 ML above the wetting layer. The solid and dash-dotted lines are smooth fitting lines to the data points. (b) The two size distributions in (a) can be scaled into nearly identical distributions. The solid curve is the theoretical scaling function of three-atom critical size.

S.H. Chang, W.B. Su, W.B. Jian, C.S. Chang, L.J. Chen, and T.T. Tsong, PRB 65, 245401 (2002)

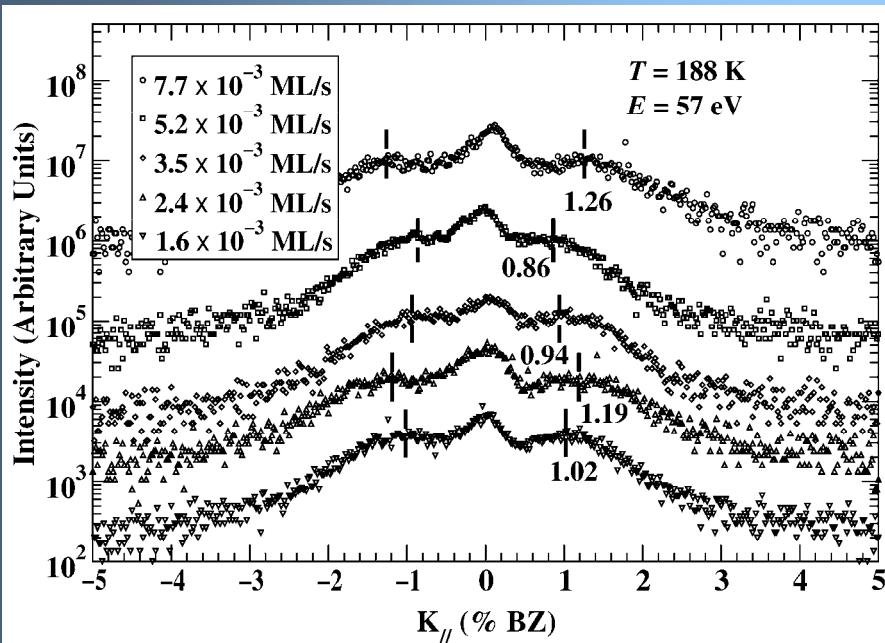
W.B. Su, S.H. Chang, H.Y. Lin, Y.P. Chiu, T.Y. Fu, C.S. Chang, and T.T. Tsong, PRB 68, 033405 (2003)

SPA-LEED measurements

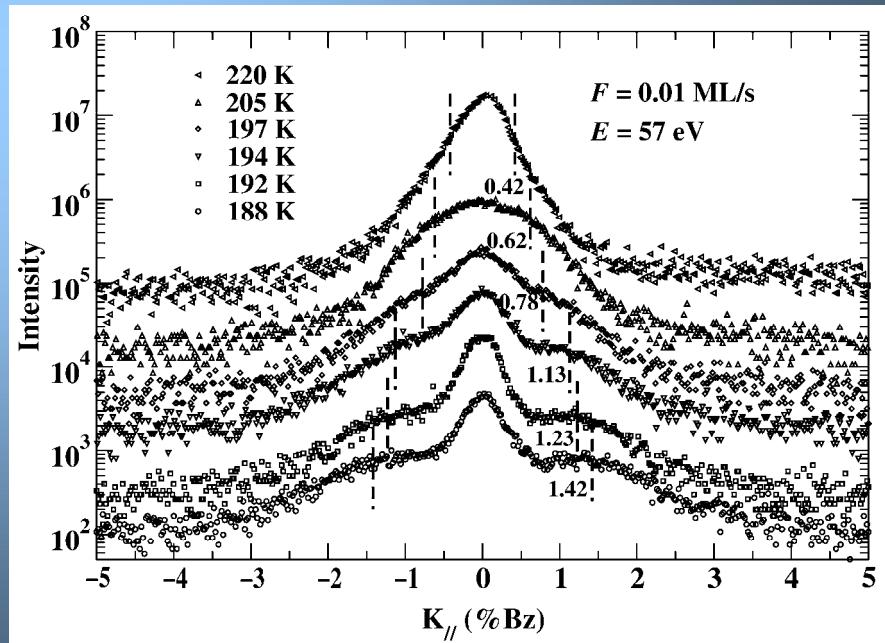
$$n_x \approx \left(\frac{1}{S} \right)^2 = \left(\frac{K_1}{2\pi} \right)^2 = \left(\frac{K_1}{K_{10}} \right)^2 \left(\frac{1}{a_0} \right)^2$$

Assumption

Measured island density = saturation density



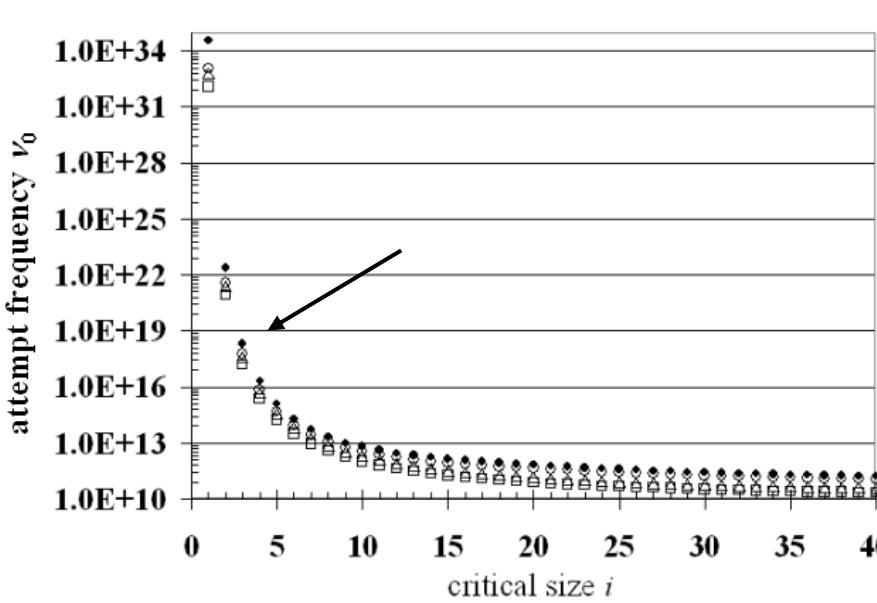
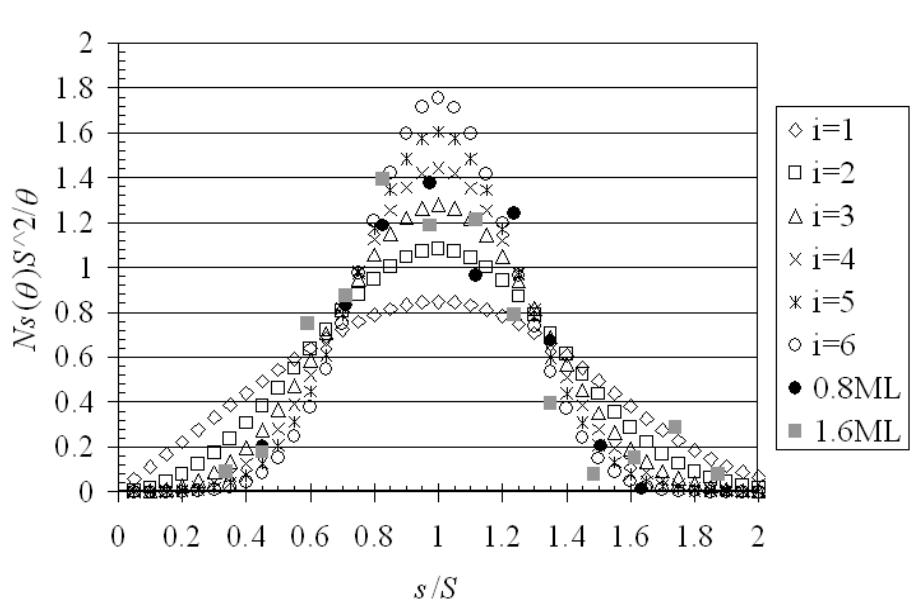
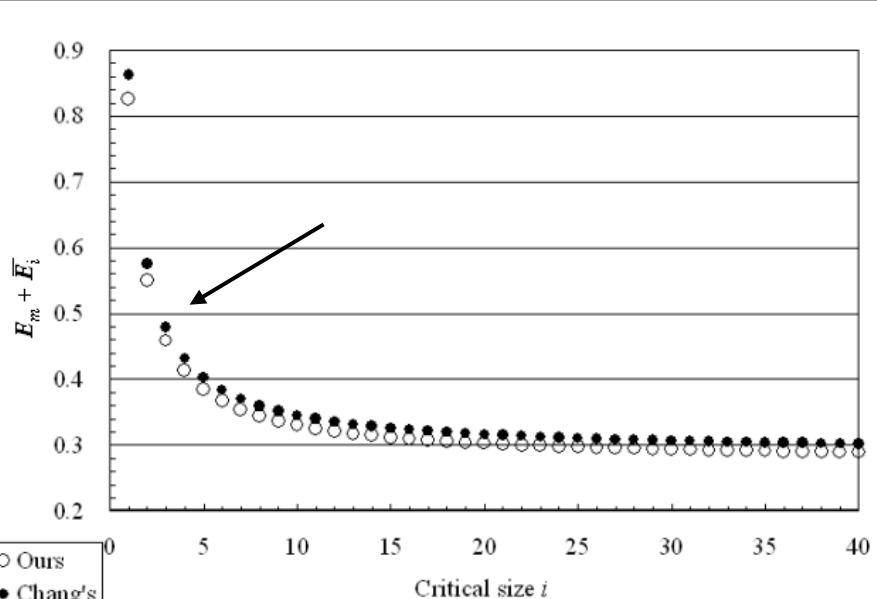
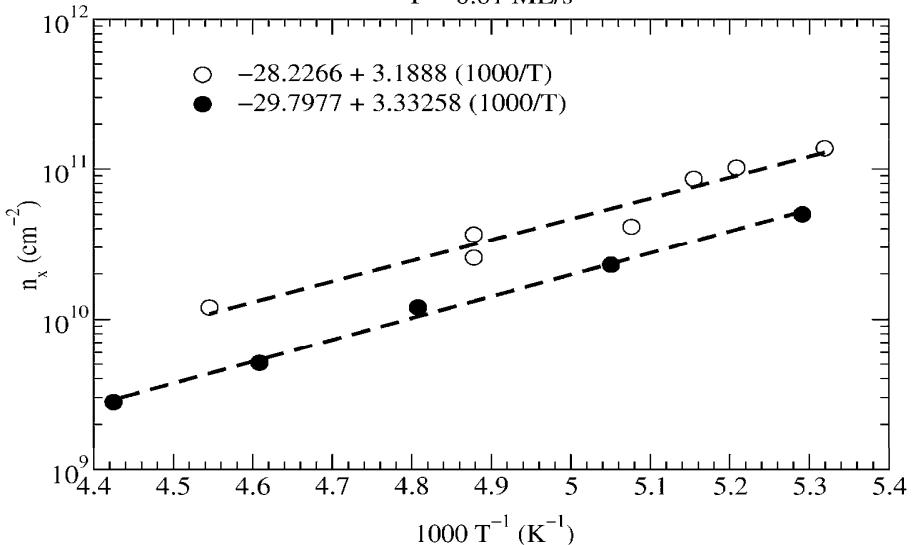
Rate dependence



Temperature dependence

Temperature dependence of island number density

$F \sim 0.01 \text{ ML/s}$



Low θ Structures

$\sqrt{3} \times \sqrt{3} - \beta$ $\sqrt{7} \times \sqrt{3}$

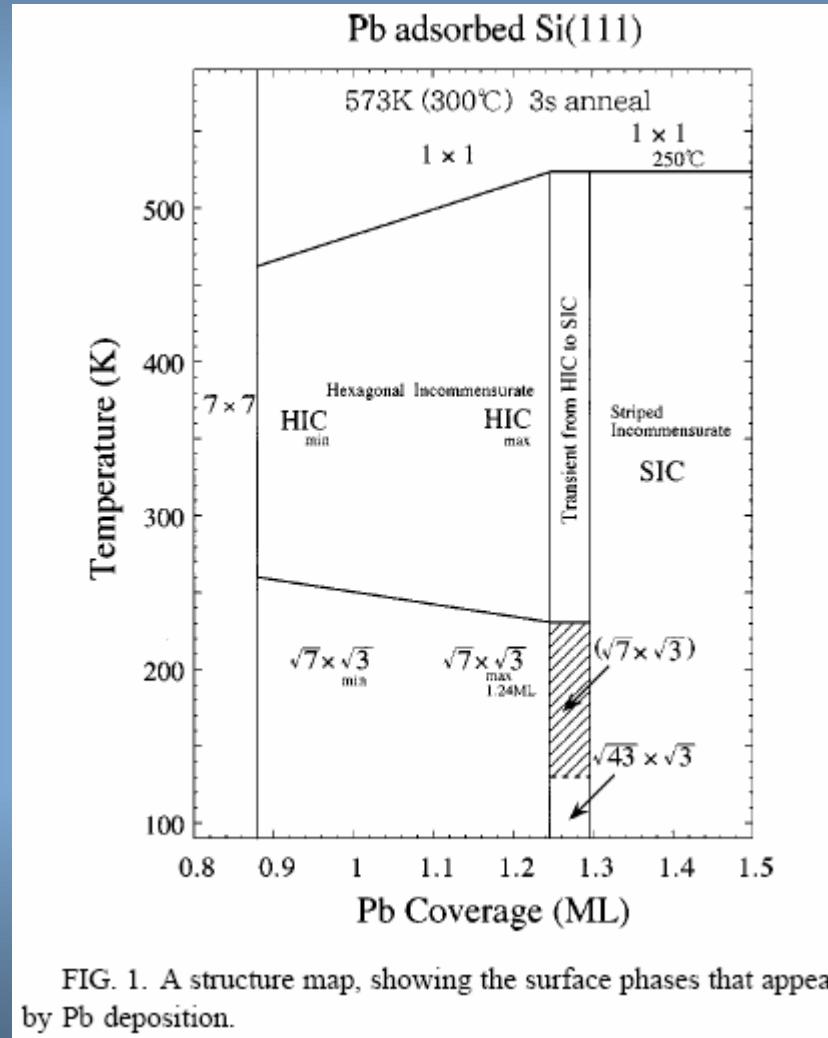
$\sqrt{43} \times \sqrt{3}$

$\sqrt{3} \times \sqrt{3} - \text{HIC}$ $\sqrt{3} \times \sqrt{3} - \text{SIC}$

Anything else?

Low coverage structures

Inconsistent results between different works



STM study on HIC phase

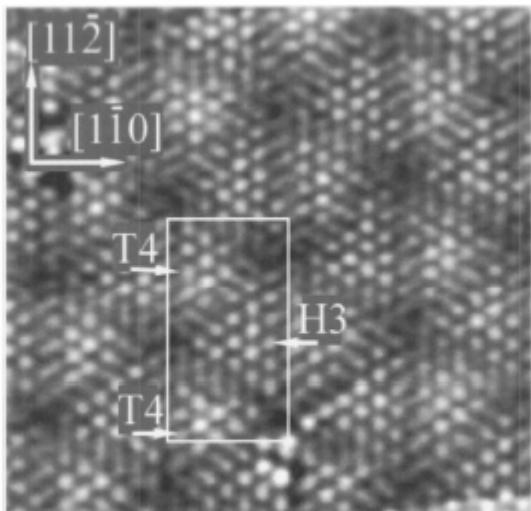


FIG. 1. 17.5 nm×15 nm STM image of the HIC phase showing the sixfold domain degeneracy, with alternating triangular domains occupying different binding sites H3 vs T4.

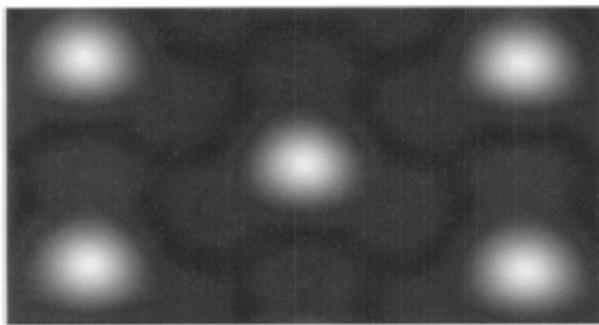


FIG. 3. First-principles calculation of the STM image of the $\alpha-\sqrt{3}\times\sqrt{3}$ for H3 site occupation with $V=+1.5$ V.

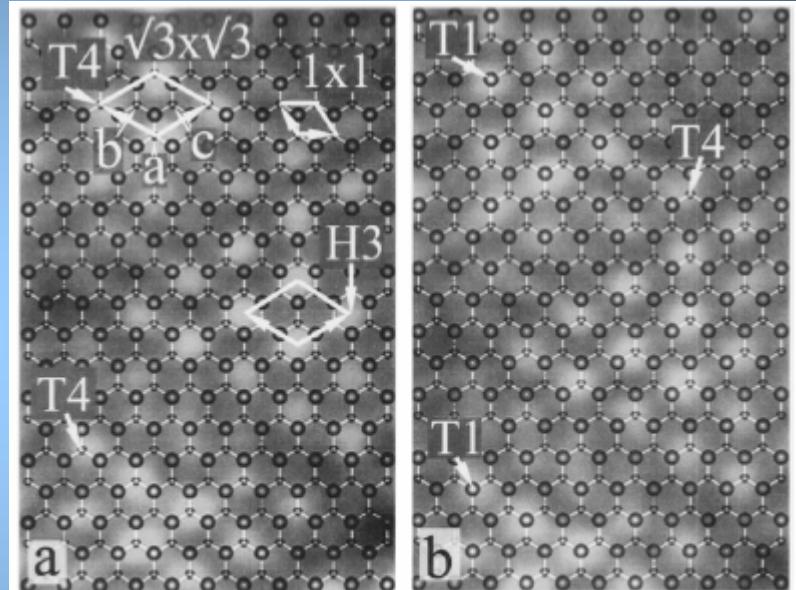


FIG. 2. A Si(1×1) lattice overlayed on top of the area in Fig. 1 enclosed by the white rectangle, can be used to deduce the type of site occupied in a given triangular domain, i.e., whether H3 or T4. Figure 2(a) is the correct assignment.

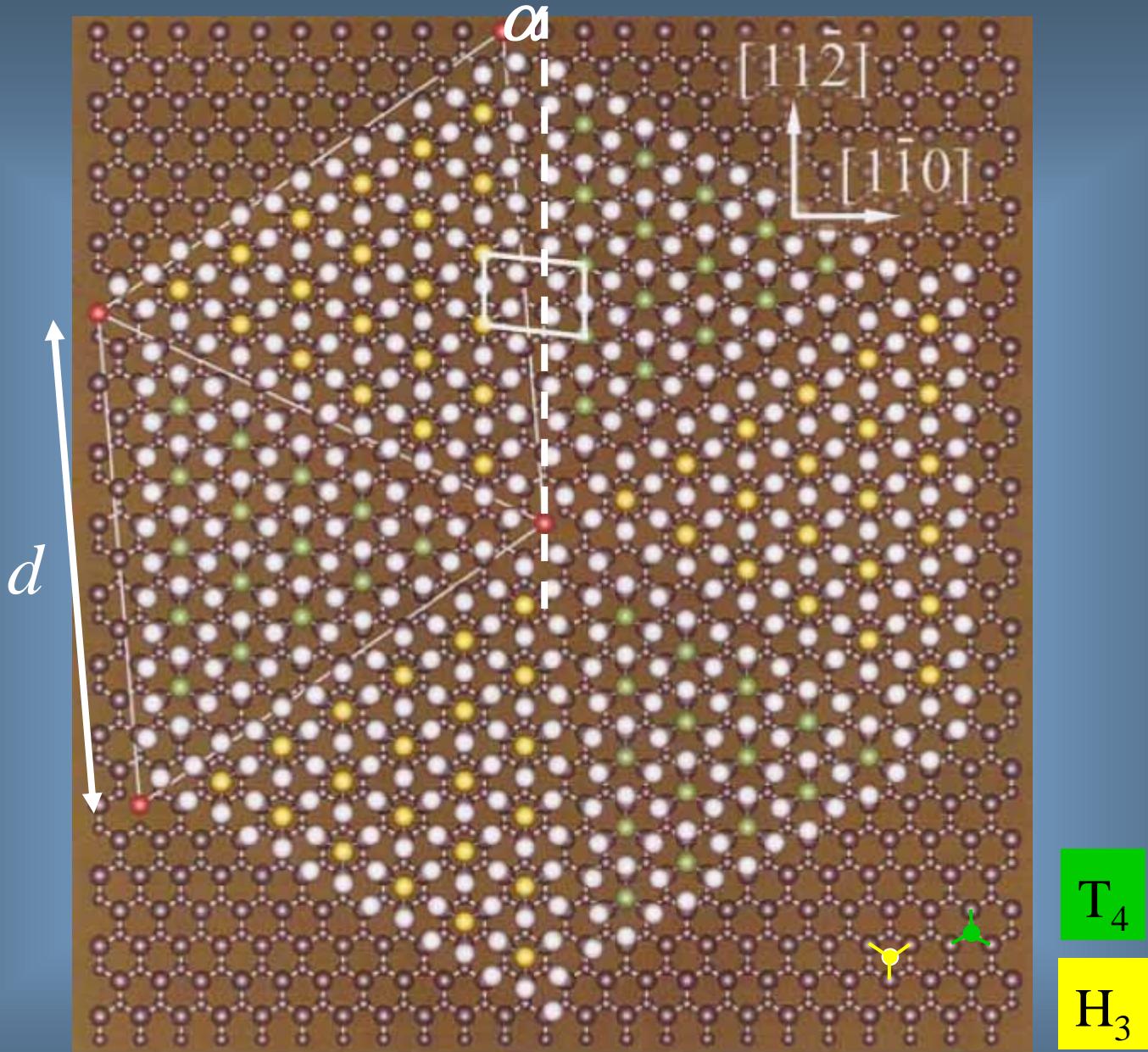


FIG. 4. (Color) Atomic model of the HIC phase shown in Fig. 1.

LEED study on HIC phase

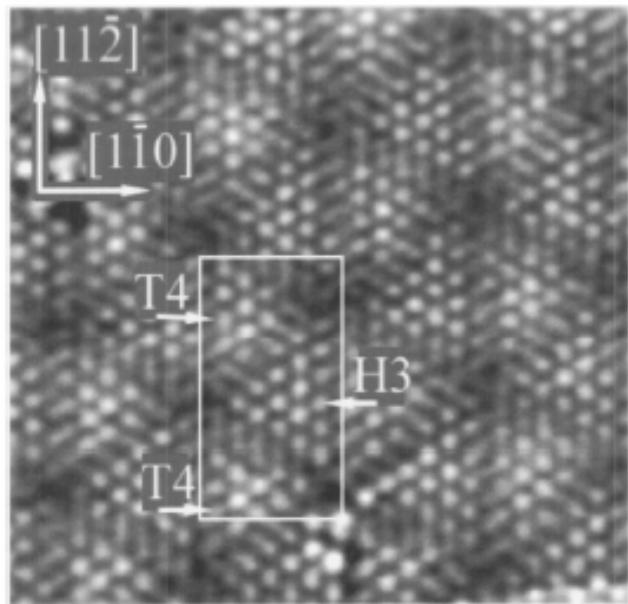
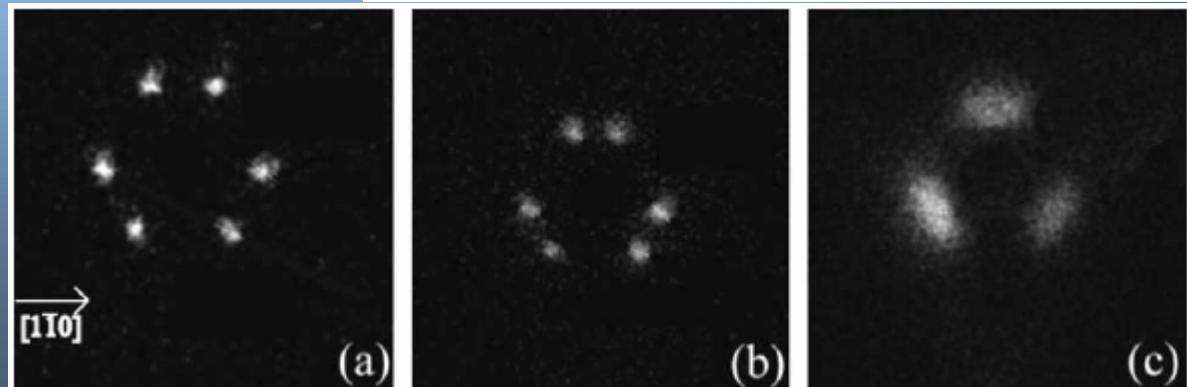
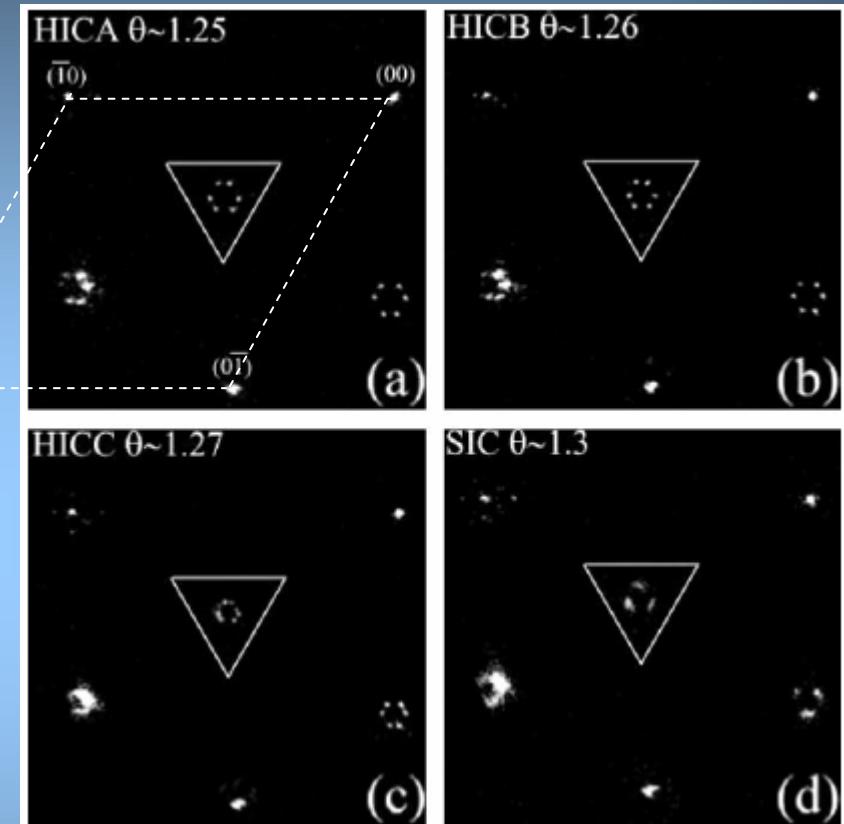
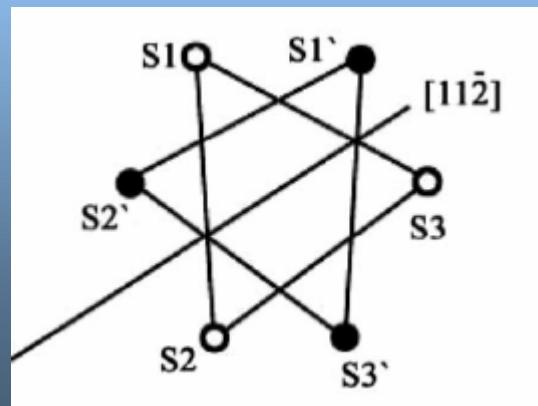
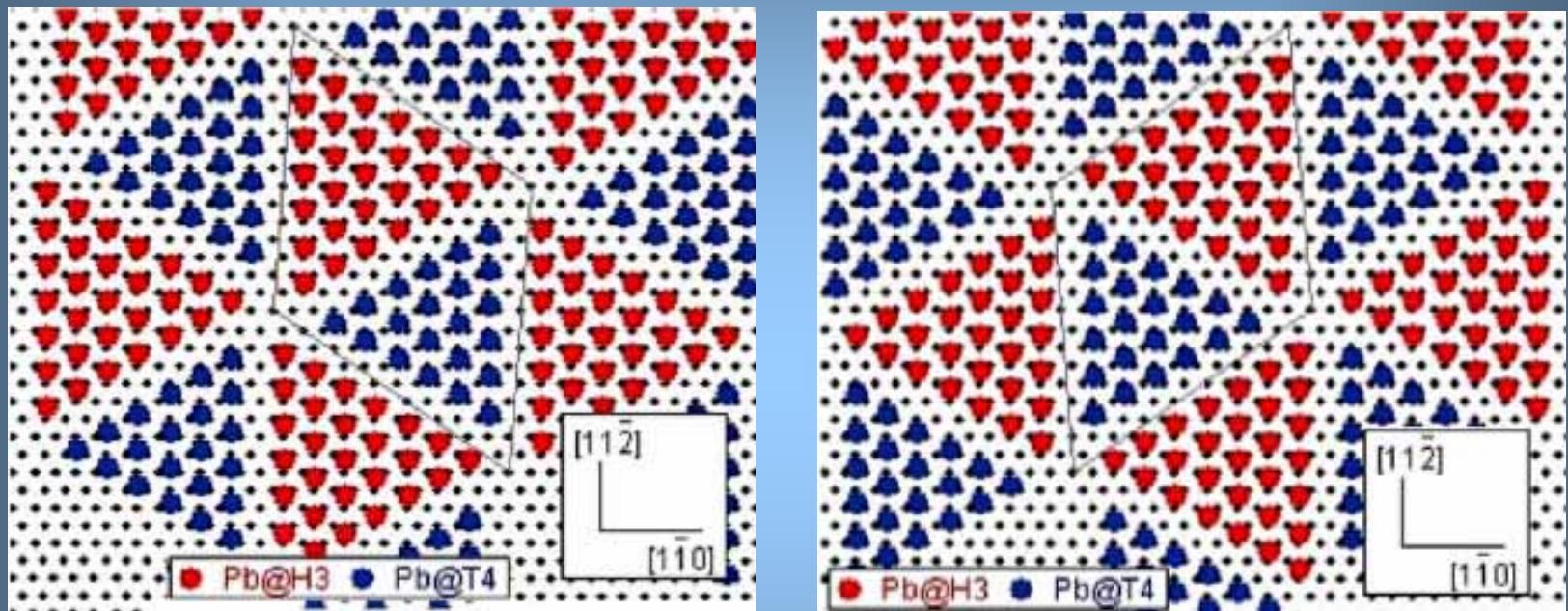


FIG. 1. 17.5 nm×15 nm STM image of the HIC phase showing the sixfold domain degeneracy, with alternating triangular domains occupying different binding sites H3 vs T4.



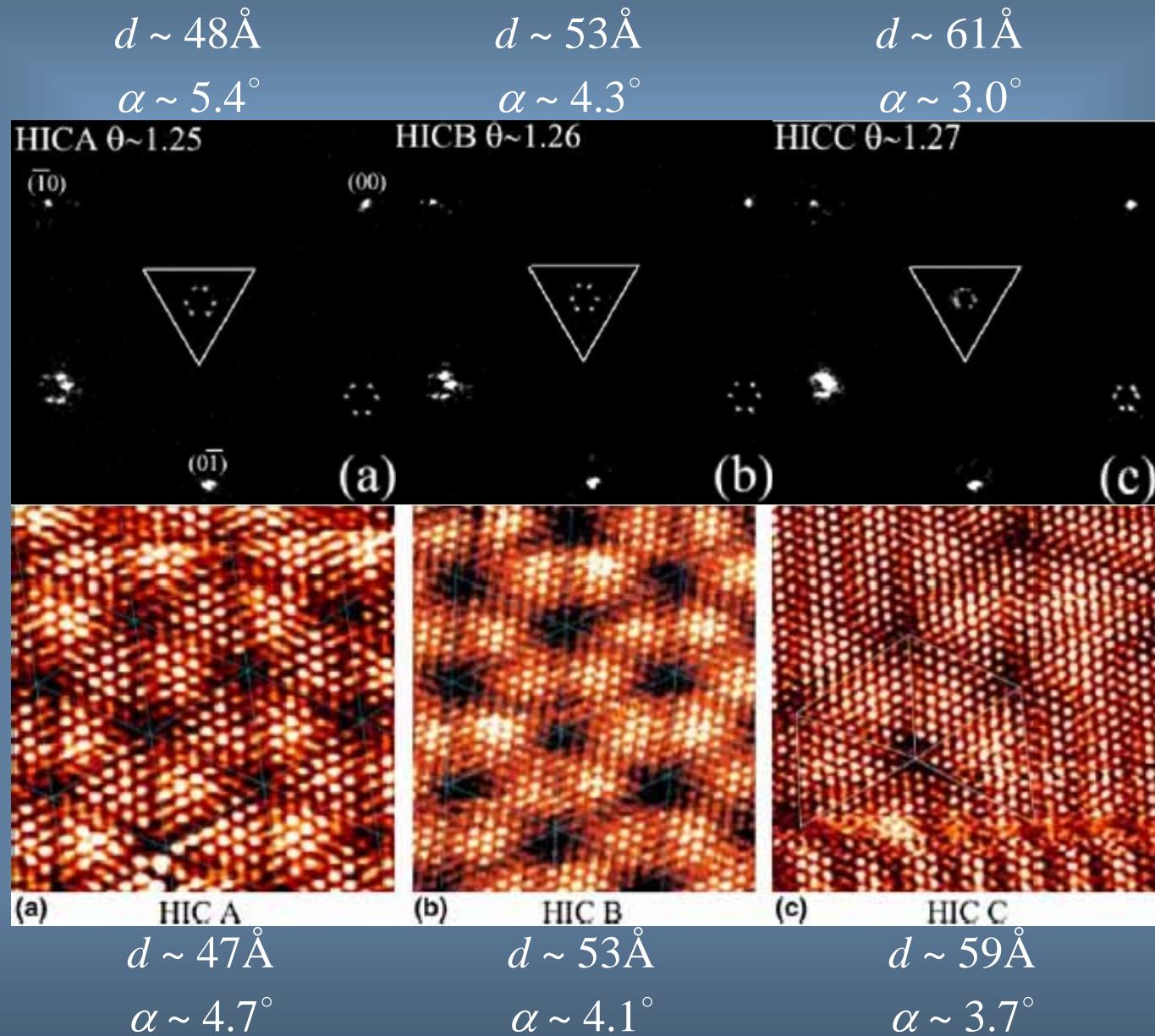
S. Stepanovskyy, M. Yakes, V. Yeh,
M. Hupalo and M.C. Tringides, Surface
Science 600, 1417 (2006)

Kinematical calculations of LEED pattern for HIC phase



S. Stepanovskyy, M. Yakes, V. Yeh,
M. Hupalo and M.C. Tringides, Surface
Science 600, 1417 (2006)

Three HIC phases



$$\sqrt{43} \times \sqrt{3} ?$$

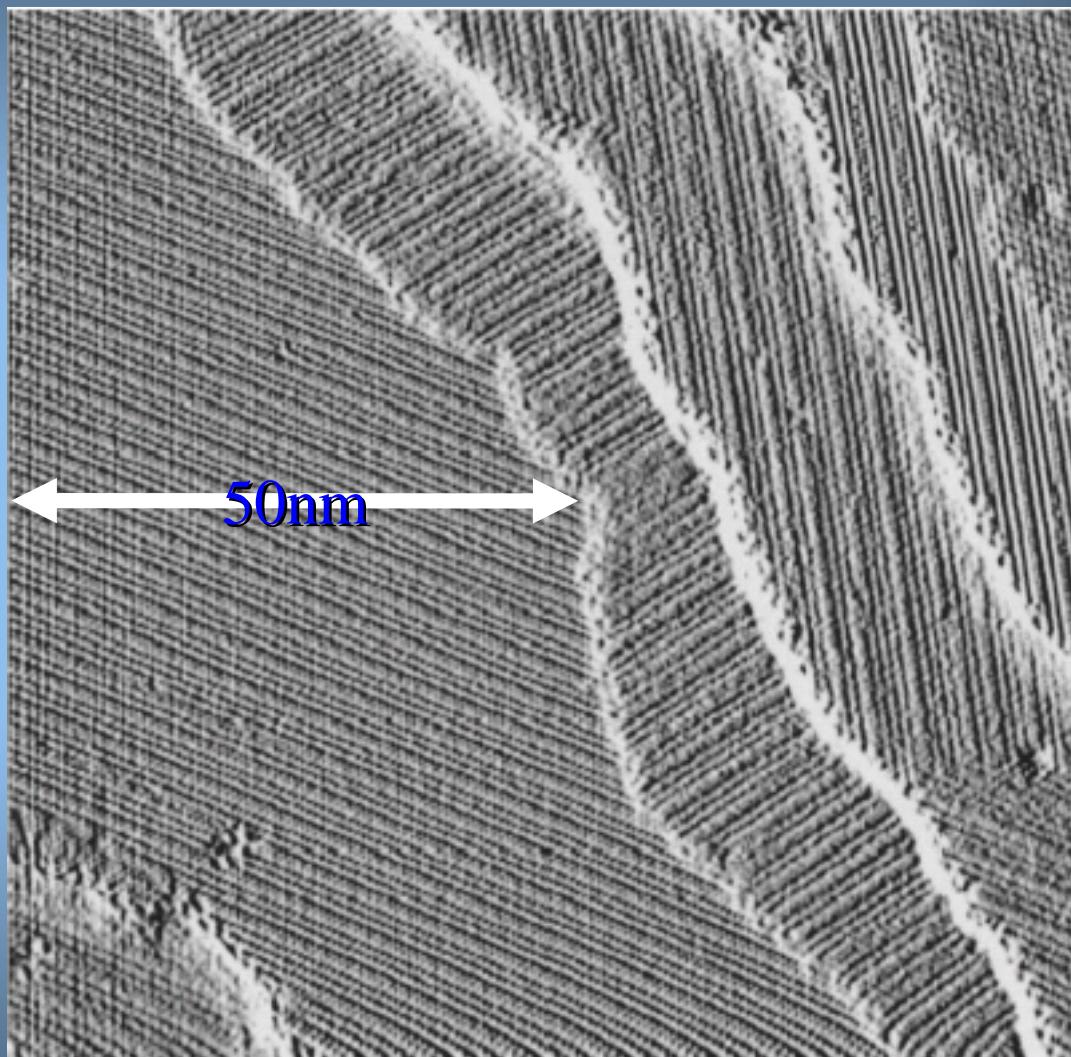
In Pb/Si(111)

$\Delta\theta = 0.006\text{ML}$

$T_{dep} = 120K$

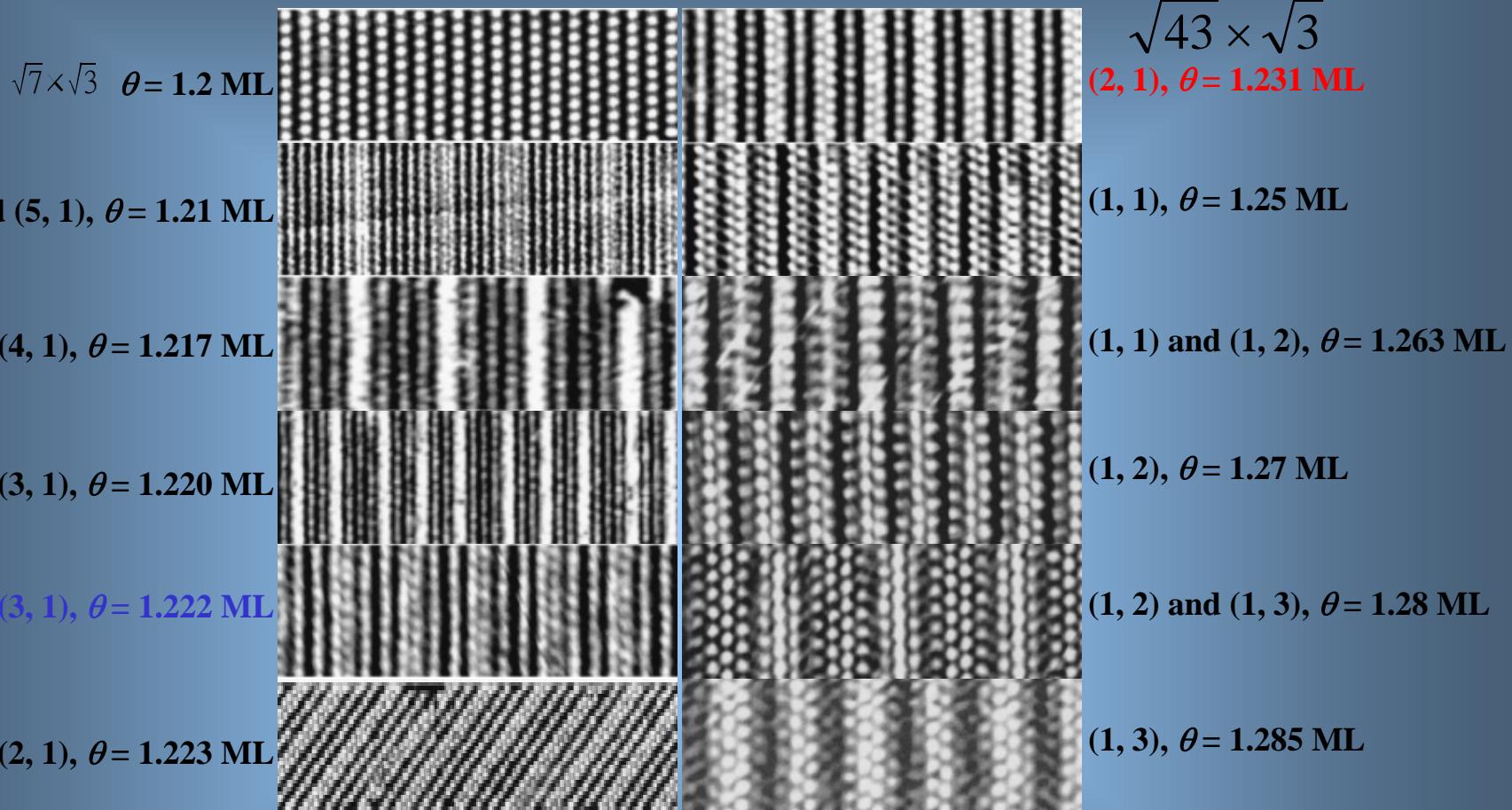
*Huge
number of
atoms move
collectively*

*Two phases
covers 80%
of 0.5mm*



1.5V, 100nm \times 100nm

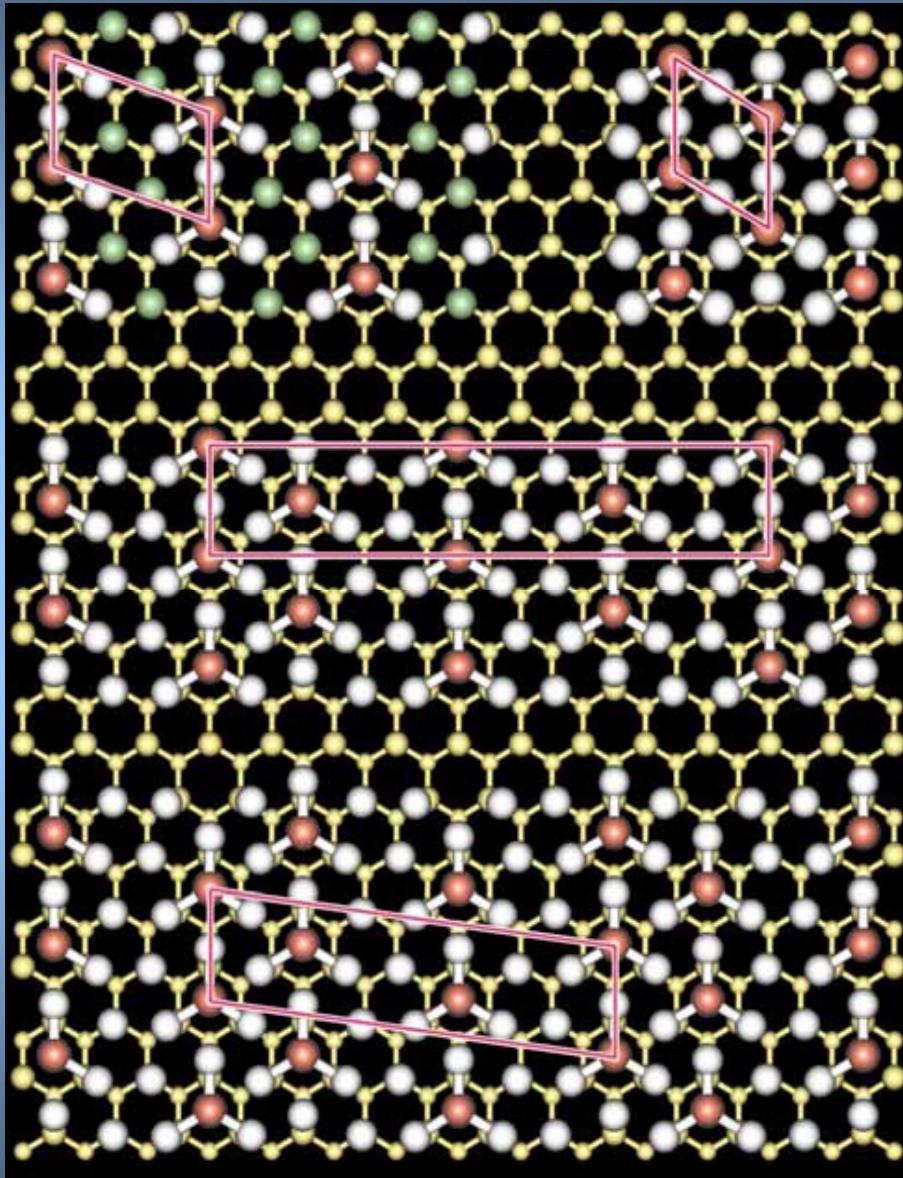
In a tiny change of θ



M. Hupalo, J. Schmalian, M.C. Tringides, PRL 90, 216106-1 (2003)

STM images of twelve distinct, commensurate phases observed within a small coverage range $1.2 \text{ ML} < \theta < 1.3 \text{ ML}$.

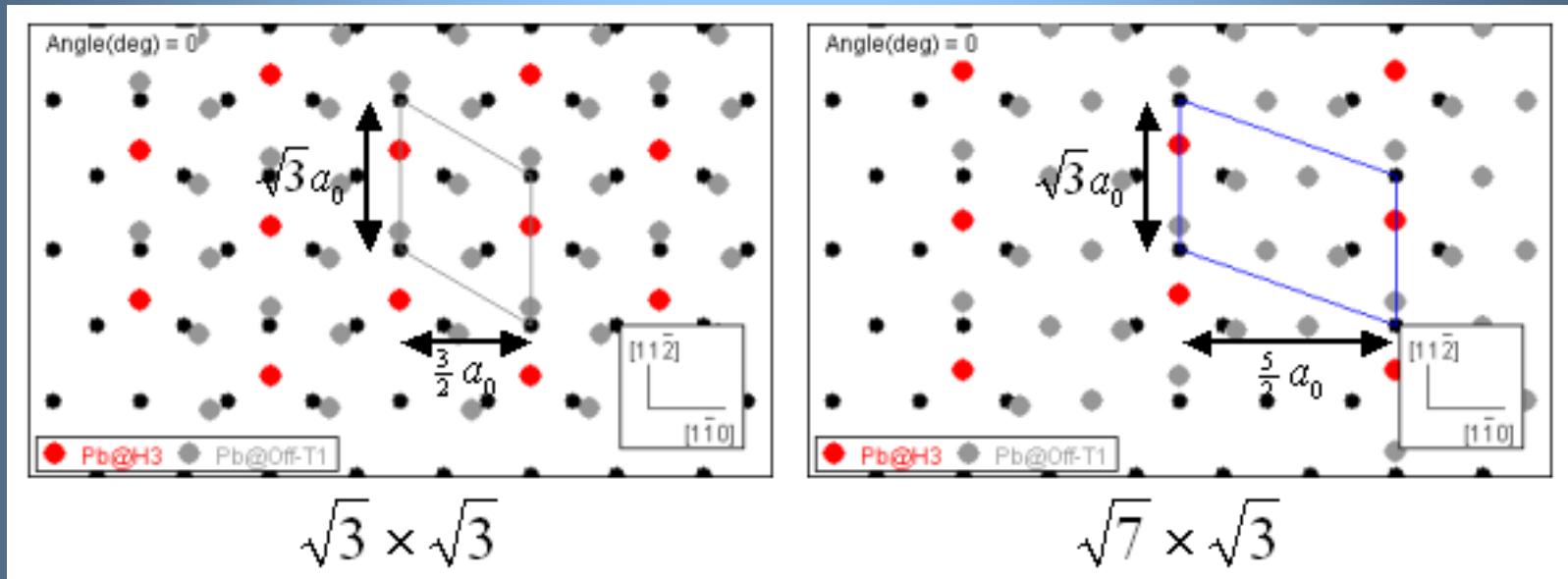
Detailed structures of $(3, 1)$ and $(2, 1)$ phases



What are the detailed structures of those separations?

Smaller separations
 $\Theta = 4/3 \text{ ML}$

Larger separations
 $\Theta = 6/5 \text{ ML}$



C.Kumpf, etc., Ssurf. Sci. **448**, L213 (2000)
T.L. Chan, etc., Phys. Rev. B **68**, 45410 (2003)

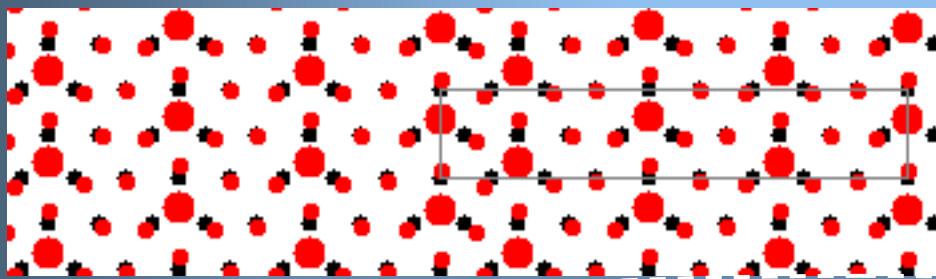
$$a_0 = 3.84 \text{\AA}$$

Periodicity and coverage of a (n, m) phase

Periodicity

$$q_{(n,m)} = (5 \times n + 3 \times m) \frac{a_0}{2}$$

For example, $(n, m) = (3, 1)$



Coverage

$$\begin{aligned}\theta_{(n,m)} &= \frac{6n + 4m}{5n + 3m} \\ &= 1 + \frac{n + m}{5n + 3m} = 1 + \frac{p}{q}\end{aligned}$$

$$q_{(3,1)} = (5 \times 3 + 3 \times 1 = 18) \frac{a_0}{2}$$

$$\theta_{(3,1)} = 1 + \frac{(3+1)}{q} = 1 + \frac{4}{18}$$

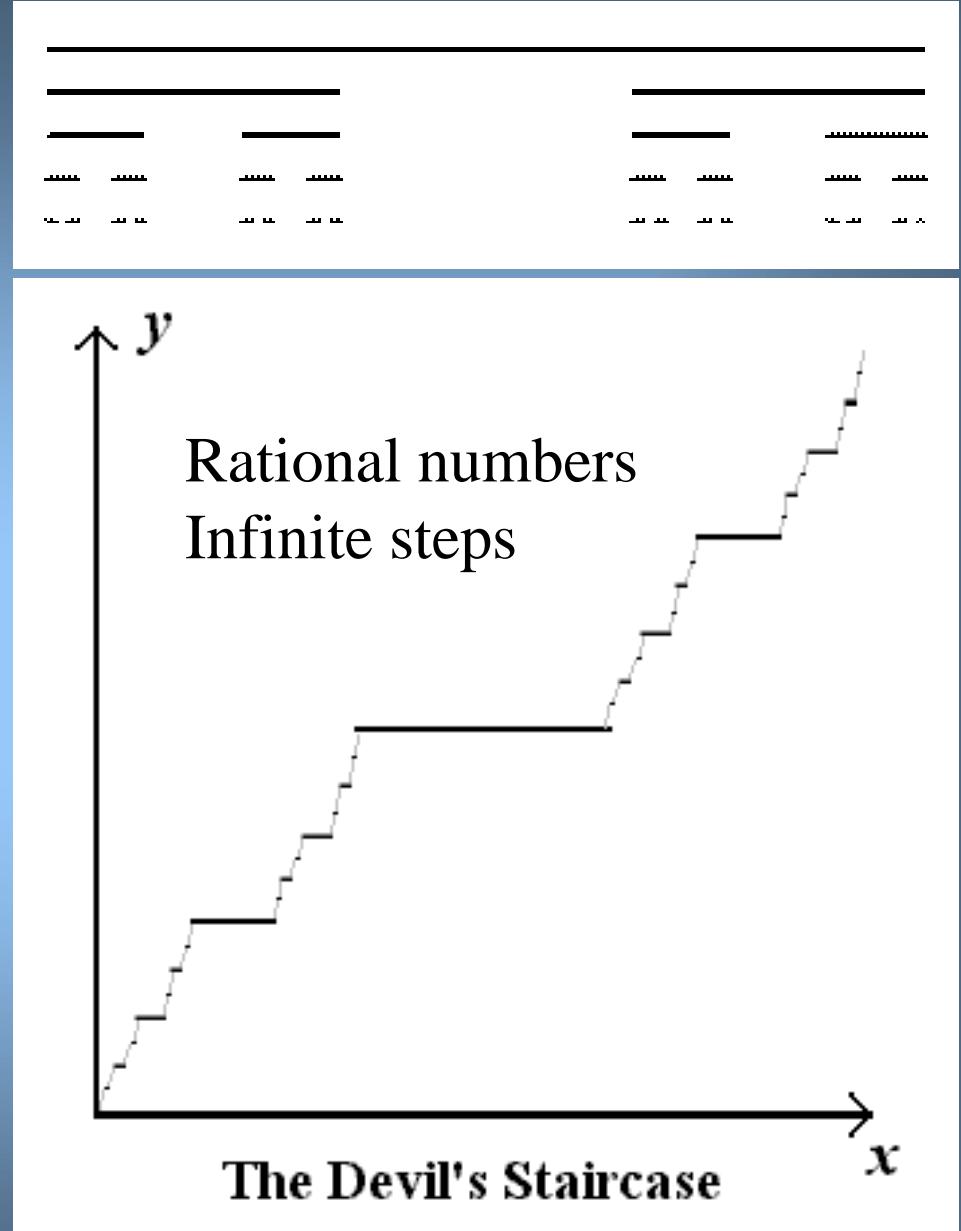
$$\theta_{(3,1)} \left(= \frac{22}{18} \right) \oplus \theta_{(2,1)} \left(= \frac{16}{13} \right) = \theta_{(5,2)=(3,1)\oplus(2,1)} \left(= \frac{38}{31} \right)$$

Cantor comb

Cantor function

Infinite steps in
a finite interval

All steps take
rational numbers



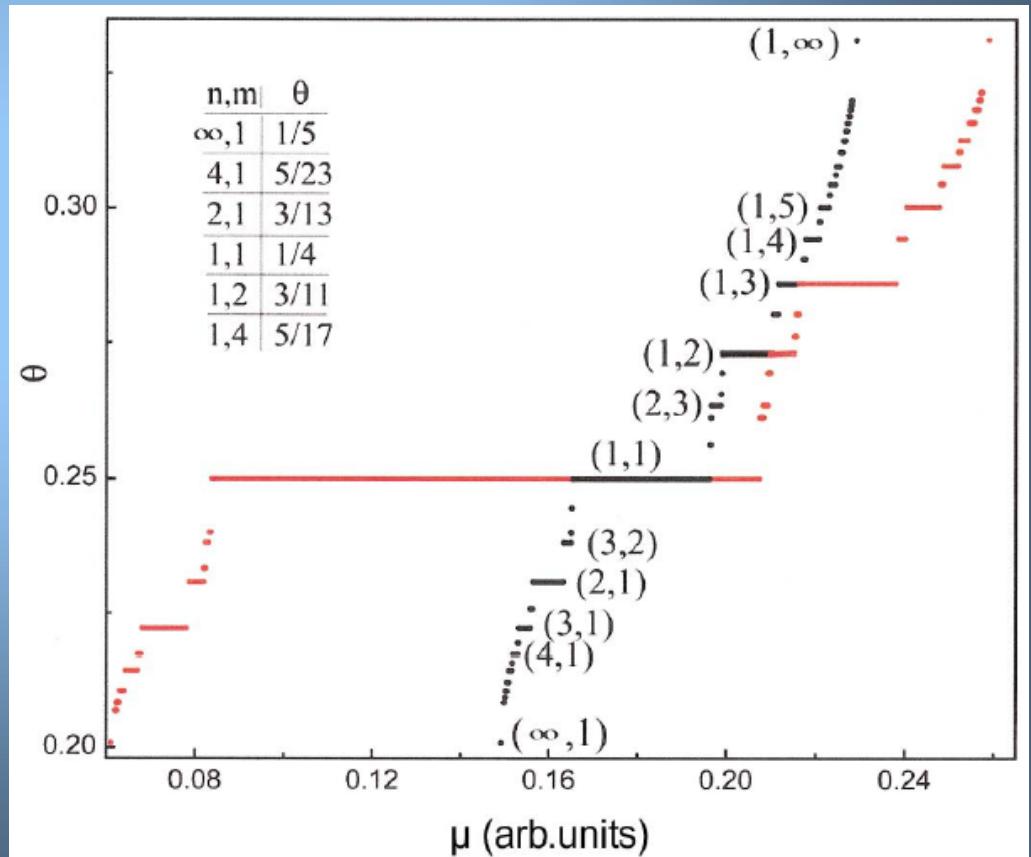
The devil's staircase in Pb/Si(111) reveals itself in θ vs μ stability curve

$$\Delta\mu(p/q) = \frac{1}{2} \sum_{l=1}^{\infty} lq \{ J(lq + 2) + J(lq - 2) - 2J(lq) \}$$

Competing interactions
Chemical: immiscibility
Elastic: lattice mismatch

*Steeper steps due to
double separation*

*Additional 3-fold
rotational symmetry
gives rise to phases other
than the DS phases at
finite temperatures*



Examples of physical systems that show a devil's staircase (I)

Competing interactions

Ferromagnetic for NN

Anti-ferromagnetic for NNN

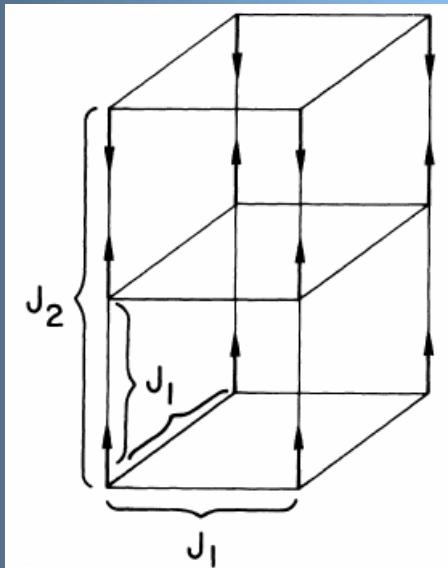
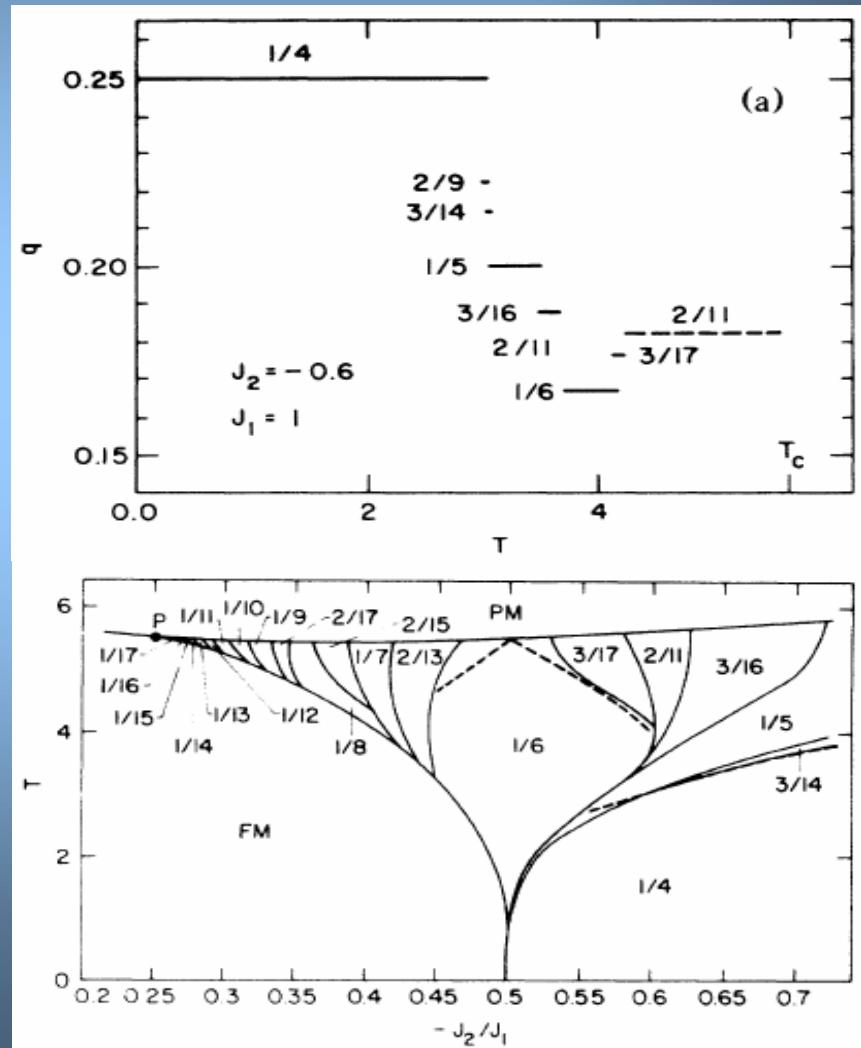


FIG. 1. Ising model with competing interactions.

Per Bak, J. von Boehm, PRB **21**, 5297 (1980)

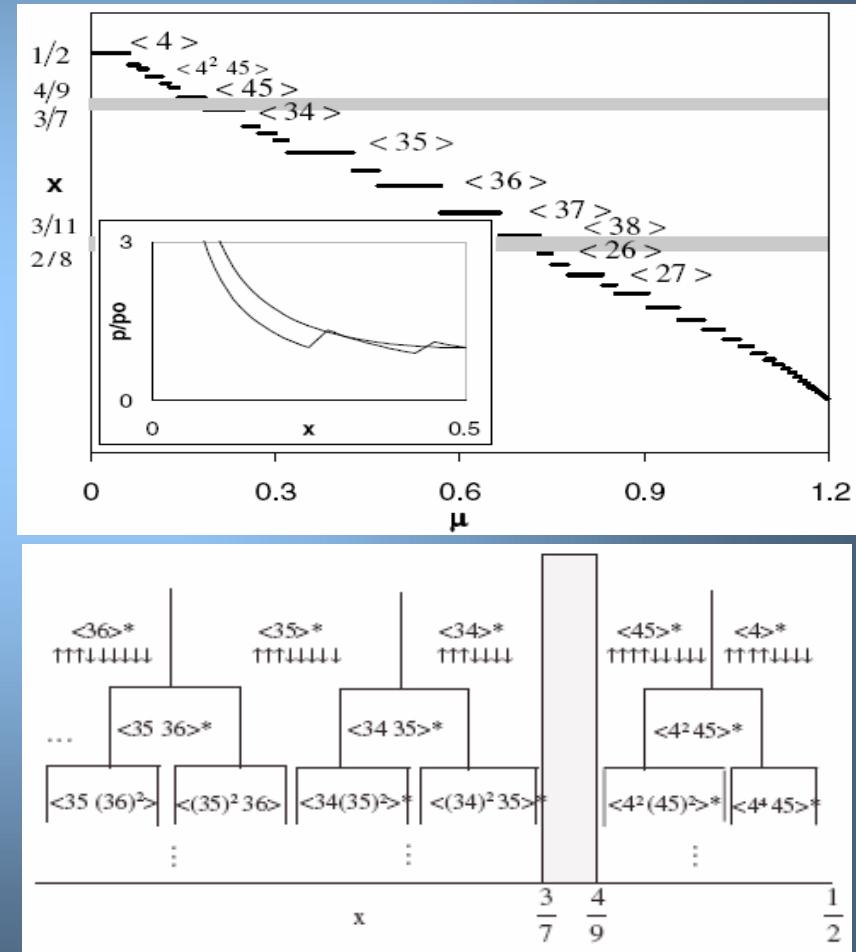
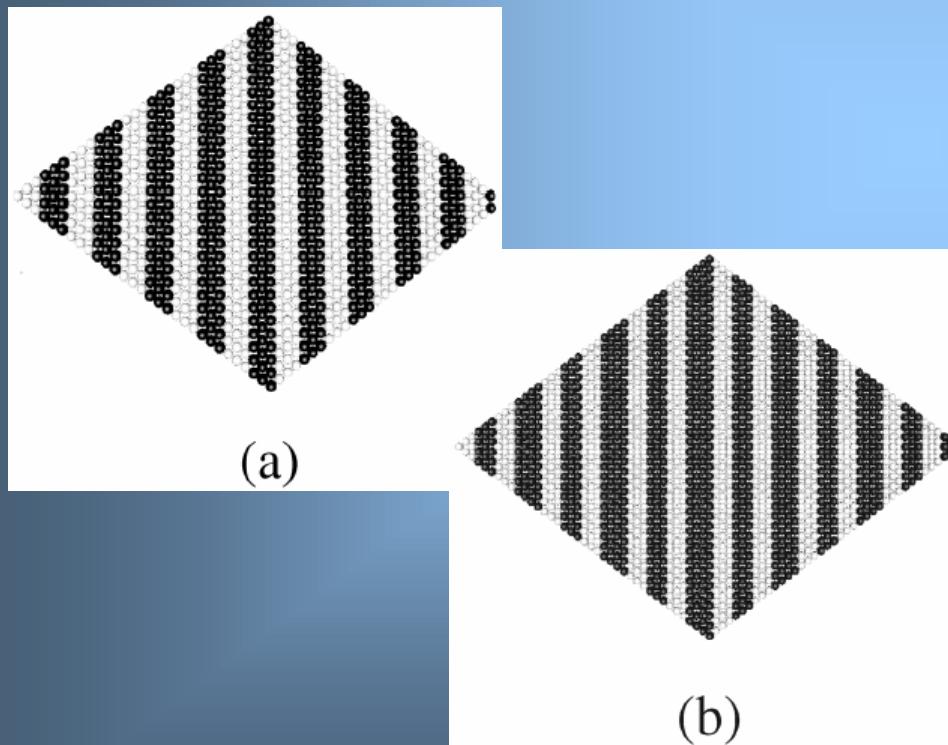


Examples of physical systems that show a devil's staircase (II)

Competing interactions

Chemical: bulk immiscibility

Elastic: lattice mismatch



Pb adsorbed Si(111)

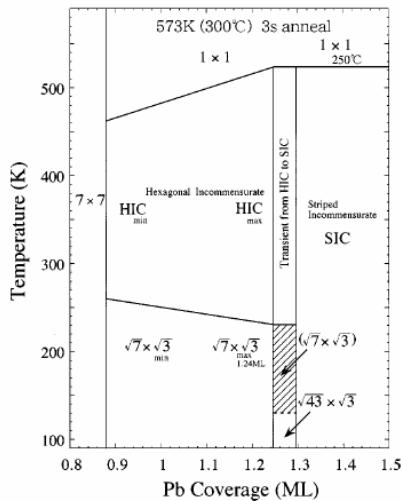
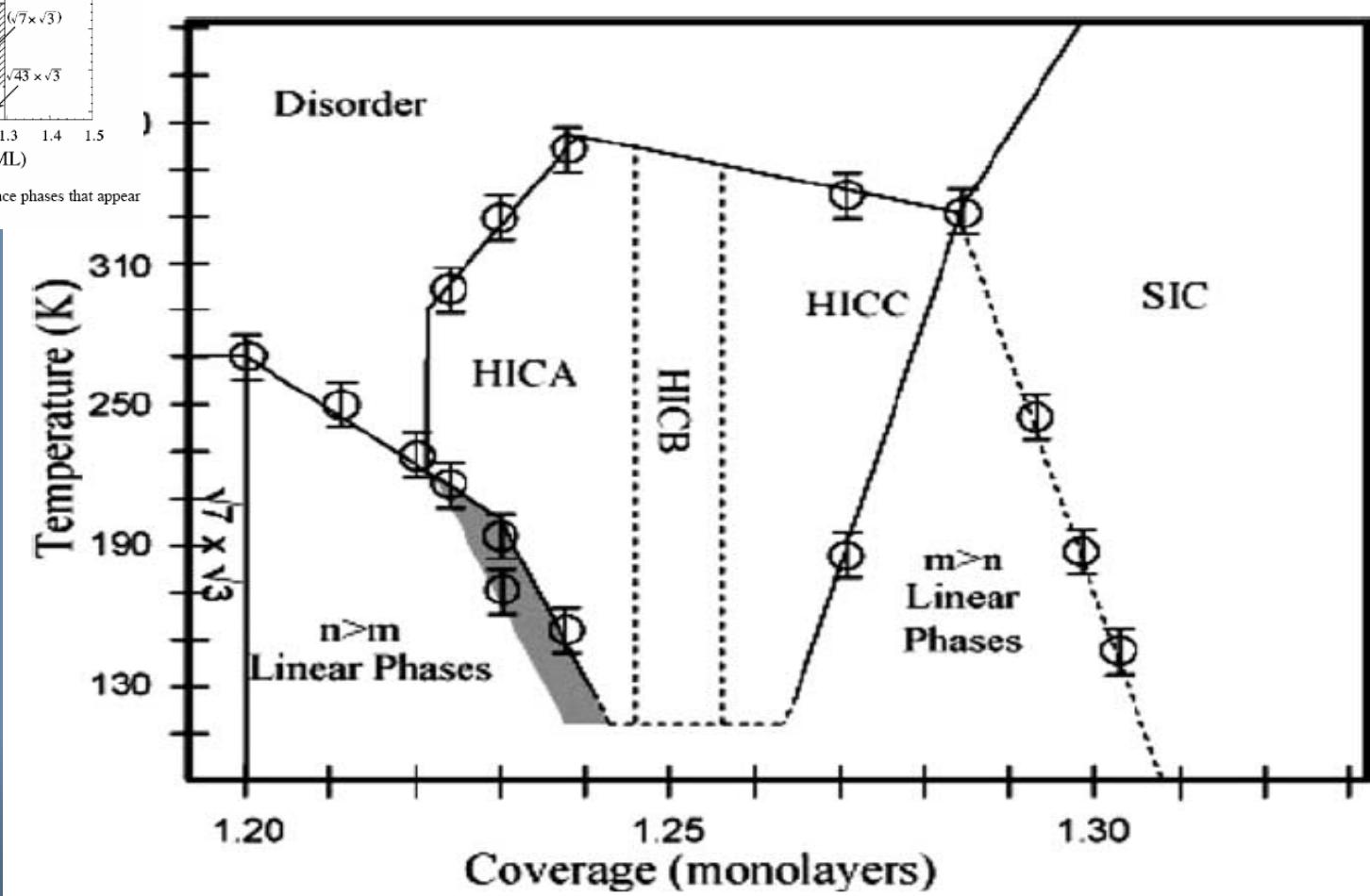


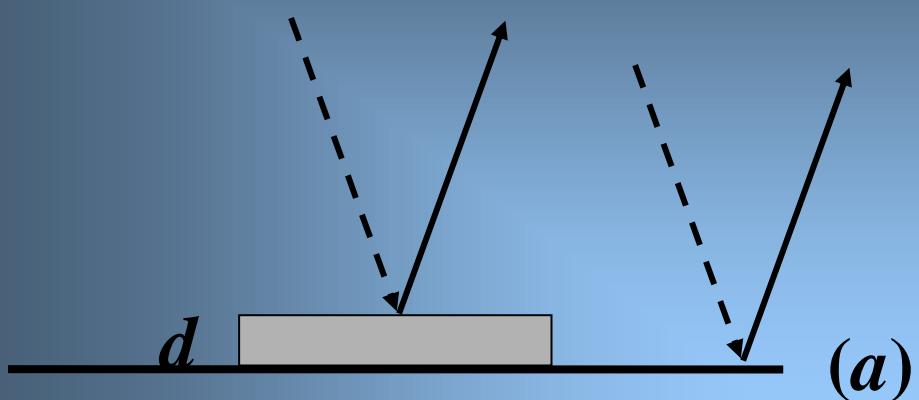
FIG. 1. A structure map, showing the surface phases that appear by Pb deposition.

The T - θ phase diagram

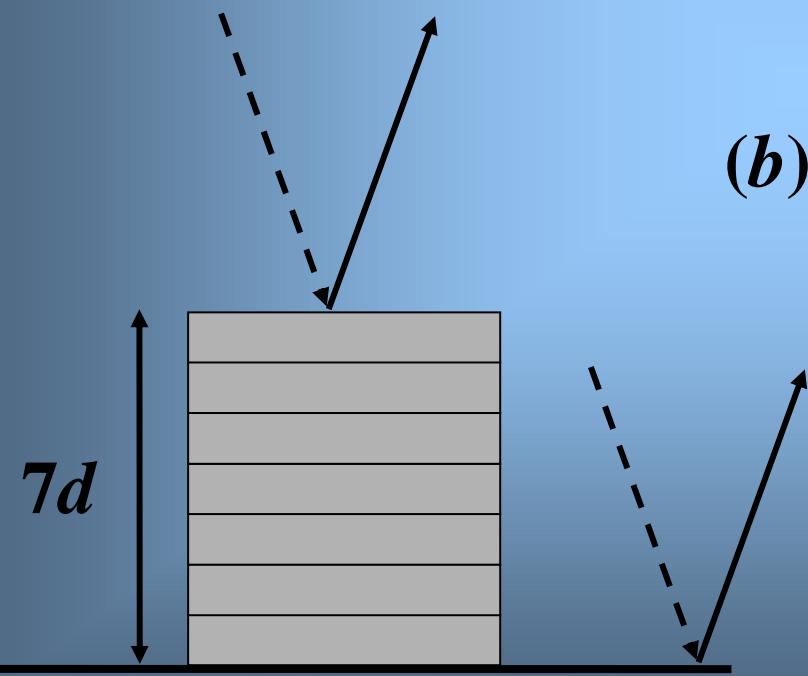


Thank you
for
your attention.

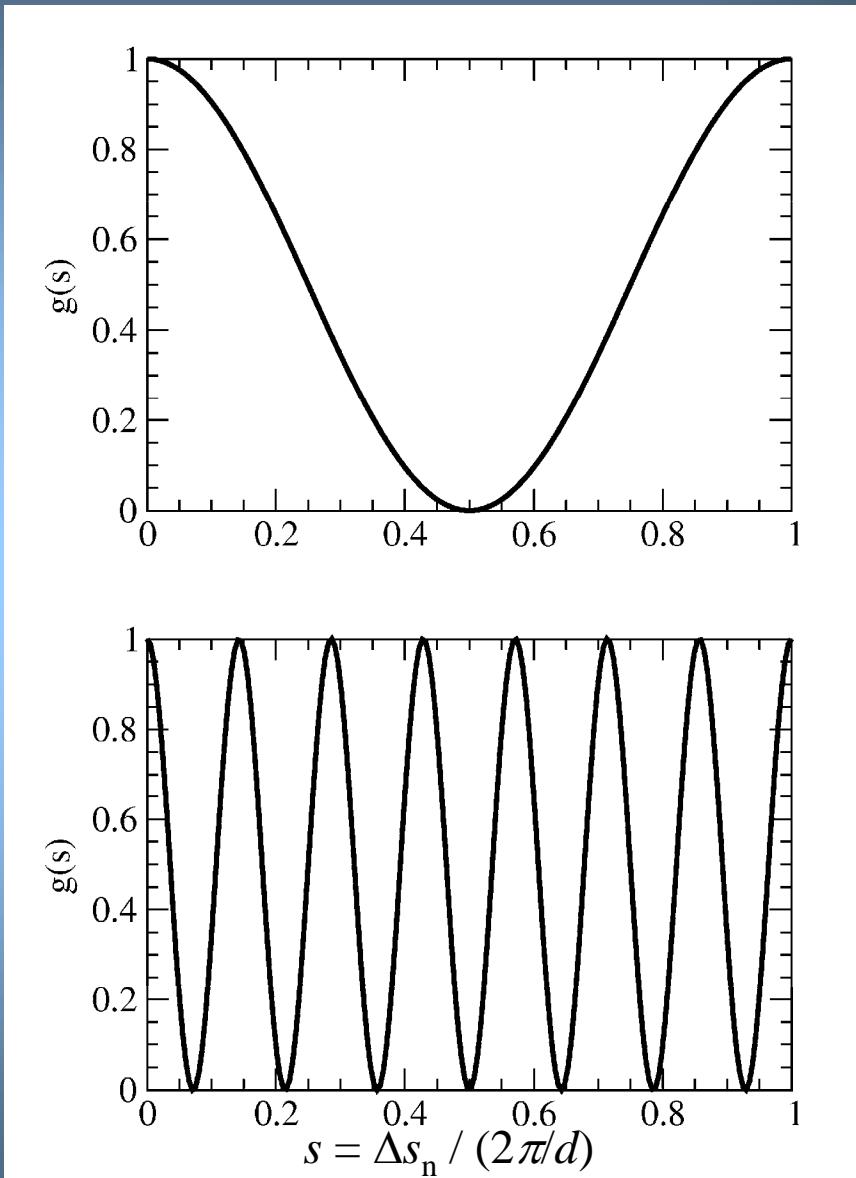
$g(s)$: Intensity of (00) spot vs electron beam energy



(a)

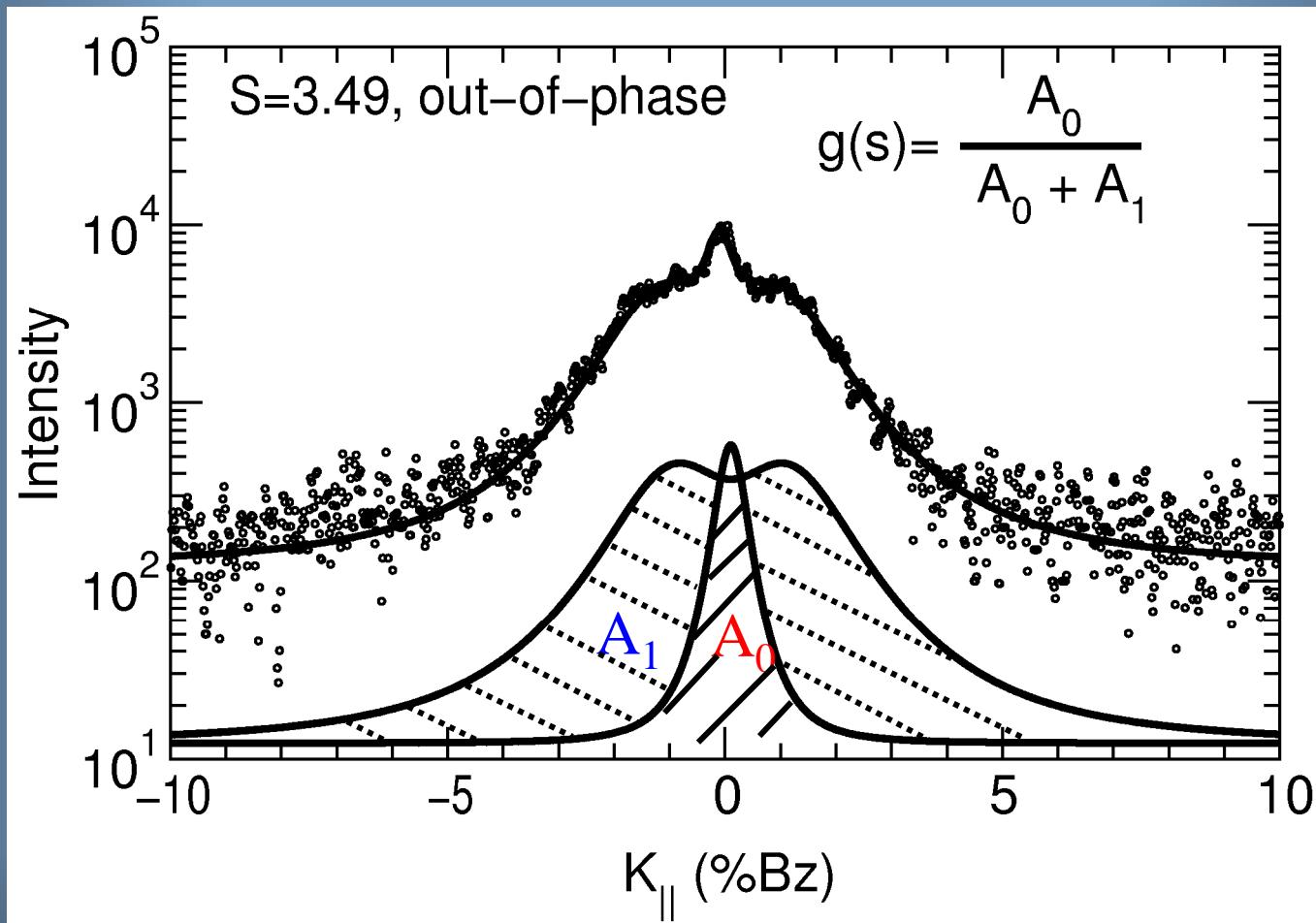


(b)



Δs_n : normal component of momentum of incident waves

$g(s)$ definition



Binary phase diagram Pb vs Si

